Electric polarization and magnetization in metals

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A feature of the modern theory of polarization is that metallic systems do not admit a well-defined ground state polarization. This is predicated on the assumption that the electronic contribution to the polarization is well-defined if and only if the electronic ground state is “localized”. If instead one takes the view that the electronic polarization is more fundamentally related to the existence of a complete set of exponentially localized Wannier functions, a definition is always admitted. This is the perspective we have adopted in the unified theory of microscopic polarization and magnetization fields that we have previously developed. Interestingly, when the modern theory admits a well-defined polarization, in particular for “trivial” insulators, these philosophically different approaches agree. Comparison with the modern theory of magnetization is somewhat different; we find agreement for the ground state orbital magnetization in “trivial” insulators and as well the predicted magnetoelectric effect, but disagree with later thermodynamic extensions to include metals and Chern insulators in that description. In addition, we also provide a novel perspective on the distinct contributions to the electrical conductivity tensor in the long-wavelength limit. In particular we find that, in the absence of any scattering mechanisms, the dc divergence of that tensor arises from what we identify as a free current density and the finite-frequency generalization of the anomalous Hall contribution arises from a combination of bound and free current densities.

I. INTRODUCTION

In elementary classical electrodynamics, the macroscopic charge and current densities in material media are written in terms of a polarization field \( \mathbf{P}(\mathbf{x},t) \), a magnetization field \( \mathbf{M}(\mathbf{x},t) \), and “free” charge and current densities \( \varrho_F(\mathbf{x},t) \) and \( \mathbf{J}_F(\mathbf{x},t) \),

\[
\varrho(\mathbf{x},t) = -\nabla \cdot \mathbf{P}(\mathbf{x},t) + \varrho_F(\mathbf{x},t),
\]

\[
\mathbf{J}(\mathbf{x},t) = \frac{\partial \mathbf{P}(\mathbf{x},t)}{\partial t} + \epsilon \nabla \times \mathbf{M}(\mathbf{x},t) + \mathbf{J}_F(\mathbf{x},t). \tag{1}
\]

The original concepts underlying the introduction of these quantities, going back to the time of Lorentz, involve notions inherent to the individual atoms and molecules that collectively compose the medium. The polarization and magnetization fields are associated with charge and current densities that remain “bound” within the individual atoms or molecules, or equivalently those charge and current densities that are localized about individual lattice sites, while the free charge and current densities are associated with the motion of carriers that are not associated with any atom or molecule and are indeed free to move through the medium.

In more modern treatments of crystalline metals and doped semiconductors, when motion of the ion cores is neglected the free charge and current densities are associated with the intraband transitions of Bloch electrons occupying eigenvectors associated with partly occupied energy bands. In the “long-wavelength limit”, where the wavelength of light is much larger than the lattice constant, the response of those carriers to the electromagnetic field is calculated as if the electric field were uniform. For example, in a too-simplistic model in which the relevant carriers are all assumed to have the same effective mass \( m_0 \), and scattering is neglected, for an applied uniform electric field oscillating at frequency \( \omega \) with amplitude \( \mathbf{E}(\omega) \) the amplitude of the uniform current density driven in linear response is given by

\[
J_F^{(1)}(\omega) = \frac{ie^2N}{m_0\omega} \mathbf{E}(\omega), \tag{2}
\]

where the superscript \( (1) \) indicates the linear response of the quantity, and \( N \) is the number of relevant carriers per unit volume.

Turning then to the other terms in the second of (1), in the long-wavelength limit the macroscopic magnetization is uniform and therefore can be neglected, and the “bound” electronic current density \( \partial \mathbf{P}(\mathbf{x},t)/\partial t \) is associated with the interband transitions of Bloch electrons associated with any occupied or partly occupied energy band. The simplest procedure, even more elementary than a Kubo approach, is to calculate the interband absorption rate using Fermi’s Golden Rule, and associate that absorption with the absorption that would result from a model in which the polarization responded to the electric field through a dielectric tensor \( \epsilon^{il} + \epsilon^{il}_{\text{inter}}(\omega) \), which would give

\[
P^{(1)}(\omega) = \frac{1}{4\pi} \epsilon^{il}_{\text{inter}}(\omega) \mathbf{E}^l(\omega), \tag{3}
\]

where superscript indices indicate Cartesian components and are summed over if repeated. This association identifies the imaginary part of \( \epsilon^{il}_{\text{inter}}(\omega) \), and the real part of \( \epsilon^{il}_{\text{inter}}(\omega) \) can then be found using the Kramers-Kronig relation [1]. Using both (2) (or a less simplistic version) and (3), with \( \epsilon^{il}_{\text{inter}}(\omega) \) so determined, a calculation of the linear response in the long-wavelength limit is com-

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plete. Sometimes one even introduces an “effective” dielectric constant $\epsilon_{\text{eff}}(\omega)$, formally writing the linear response $J^{(1)}(t)$ of the full current density from the second of (1) as just $J^{(1)}(t) = \partial P_{\text{eff}}^{(1)}(t)/\partial t$, with

$$P_{\text{eff}}^{(1)}(\omega) = \epsilon_{\text{eff}}(\omega) - \frac{\delta_{\text{il}}}{4\pi} E^l(\omega).$$

Then, in terms of the calculated $\epsilon_{\text{inter}}(\omega)$ and within the simple model (2) for the intraband response, we have

$$\epsilon_{\text{eff}}(\omega) = \delta_{\text{il}} + \epsilon_{\text{inter}}(\omega) - \frac{4\pi e^2 N}{m_0 \omega^2} \delta_{\text{il}}.$$

This strategy is somewhat indirect. One might suppose that the polarization would be defined, and then its response to the electric field calculated. But such a definition is bypassed by calculating $\epsilon_{\text{inter}}(\omega)$, that is, the contribution that a purported polarization would make to the optically induced current density.

Of course, the use of an approach that bypasses such definitions is not surprising. The concept of “bound” charges and their currents, and the polarization and magnetization to be associated with them, is at least initially suspect from the perspective of the quantum theory of solids: The usual simple model of the ground state is based on electrons occupying Bloch functions that extend through the infinite crystal, and how to associate local dipole moments with the perturbation of these Bloch functions that an applied field would introduce is not immediately obvious. Indeed, such problems in defining the polarization and magnetization arise even for the ground state of a crystal. For example, associating the polarization and magnetization with the electric and magnetic dipole moments of the charges in a unit cell is ambiguous, for the result depends on how the unit cell is chosen [2].

In recent years the “modern theories of polarization and magnetization” have been developed to clarify these concepts [3–5]. These theories have been a profound innovation in condensed matter theory, and have provided many physical insights, including the “quantum of ambiguity” associated with the electric polarization [6], the existence of two distinct contributions to the orbital magnetization [4, 5], and the result that a uniform dc magnetic (electric) field can induce a polarization (magnetization) in instances of sufficiently low symmetry [7, 8]. However, the approach is based on static or adiabatically varying uniform fields, and so is not immediately applicable to treat the optical properties of materials. This is especially a problem at wavelengths so small – beyond the “long-wavelength limit” – that one has to take into account the variation of the optical fields over a unit cell.

As well, the main focus of the “modern theories” has been limited to “trivial” insulators, a class of band insulators that we define below. Indeed, among the contributions of the modern theory is the notion that there may be a relationship between a certain “localization” of the electronic ground state and the unperturbed polarization [9–11], and in fact it has been argued that a “localized” ground state is a necessary condition for polarization to be a well-defined quantity. As the ground state of a metallic crystal is found to violate the criteria for this localization, it is the conclusion of the modern theory that polarization is not well-defined for such systems. In contrast, the modern theory of magnetization does not require such a “localized” ground state, and extensions of the expression for the magnetization of trivial insulators have been presented to expand the description to include Chern insulators and metals [5, 12]. These extensions are based on thermodynamic arguments and thus again are not applicable to optical fields. Indeed, there seems no straightforward roadmap for extending the approach of the “modern theories” to frequency dependent polarizations, magnetizations, and free currents.

In recent work [13] we have taken a different approach, which is related more directly to the classical strategy of Lorentz. Working under the frozen-ion approximation, we first decompose the expectation values of the electronic charge and current density operators of the material medium, $\langle \hat{\rho}(x, t) \rangle$ and $\langle \hat{j}(x, t) \rangle$, into a sum of contributions associated with each Bravais lattice vector $\mathbf{R}$ of the infinite crystal, $\rho_{\mathbf{R}}(x, t)$ and $j_{\mathbf{R}}(x, t)$ [14]. These “site quantities” are identified with the aid of a set of basis functions that are each spatially localized about a particular lattice site [15]; in crystalline solids a set of exponentially localized Wannier functions (ELWFs) is the most convenient choice. The $\rho_{\mathbf{R}}(x, t)$ and $j_{\mathbf{R}}(x, t)$ that result are well-localized spatially, and we construct preliminary electronic site polarization $\mathbf{p}_{\mathbf{R}}^{el}(x, t)$ and magnetization $\mathbf{m}_{\mathbf{R}}(x, t)$ fields from them in a manner similar to that of atomic and molecular physics [16, 17]. But unlike the limit of a molecular crystal in which electrons are taken to be confined about a particular lattice site, charge continuity does not hold site-wise in a general crystalline solid. This leads to a corrective contribution $\mathbf{m}_{\mathbf{R}}(x, t)$ to the preliminary site magnetization $\mathbf{m}_{\mathbf{R}}^{el}(x, t)$ so that in all $\mathbf{m}_{\mathbf{R}}(x, t) = \mathbf{m}_{\mathbf{R}}^{el}(x, t) + \mathbf{m}_{\mathbf{R}}(x, t)$. We also identify ionic contributions $\mathbf{p}_{\mathbf{R}}^{ion}(x)$ associated with the fixed ion cores so that in all $\mathbf{p}_{\mathbf{R}}(x, t) = \mathbf{p}_{\mathbf{R}}^{el}(x, t) + \mathbf{p}_{\mathbf{R}}^{ion}(x)$ [18]. Natural definitions for site charges and link currents emerge as well, which are used to define free site charge and current densities. Ultimately we sum these site contributions to give microscopic polarization and magnetization fields, and microscopic free charge and current densities; their spatial averages are then taken to be the analogous macroscopic fields appearing in (1).

An advantage of this approach is that there is a systematic method for identifying electric and magnetic multipole moments, and the effect of arbitrarily varying electromagnetic fields can be taken into account [19, 20]. Interestingly, for an unperturbed trivial insulator occupying its zero temperature ground state, the dipole moment of $\mathbf{m}_{\mathbf{R}}(x)$ coincides with the “atomic-like” contribution to the magnetization of the modern theory, and
the dipole moment of $\mathbf{m}_R(x)$ with the “itinerant” contribution [5, 13]; in the approach we adopt this terminology is manifestly descriptive. Moreover, in that case the dipole moment of $p_R(x)$ coincides with the polarization of the modern theory [6, 13]. In addition, we find agreement when considering the orbital magnetoelectric effect [7, 8, 19]; indeed, we can extend the treatment of the orbital magnetoelectric polarizability to finite frequencies [20]. Furthermore, this formalism is consistent with previous calculations of the effective conductivity tensor in insulators [21] as well as with the perturbation theory of multipole moments in the molecular crystal limit [20].

In this paper we extend this approach to treat the optical response of a metal. In this initial treatment we restrict ourselves to the long-wavelength limit and consider the independent particle approximation, in which the interaction between electrons is approximated treated through an effective potential energy characterizing the lattice, and by taking the “applied” electric field in our calculations to be the macroscopic Maxwell electric field, having frequency components $E(\omega)$.

Within the framework we have developed, the identification of the “site quantities” requires the existence of a general set of ELWFs, which happens to entirely depend on topological considerations. In Sec. II we briefly discuss such issues, but the result is that if a particular geometric structure, a certain Hilbert bundle, associated with an isolated set of energy bands is globally trivial in the topological sense, then the corresponding electronic eigenfunctions can be used to construct ELWFs [22, 23]. In general, it has been shown [24] that the Hilbert bundle constructed using the eigenfunctions associated with all of the energy bands is trivializable, thus a complete set of ELWFs can always be constructed. Then, within our framework, the microscopic polarization and magnetization fields, and thus their multipole moments as well, are always well-defined quantities, as are the microscopic free charge and current densities. And of course the corresponding macroscopic fields are as well. In this paper we will restrict our study to those crystalline solids for which the Hilbert bundle associated with any set of isolated energy bands – including the completely occupied and partly occupied energy bands in a p-doped semiconductor at zero temperature, which is the model of a metal we adopt in this first communication – is globally trivial; thus, the eigenfunctions associated with any set of isolated energy bands can be used to construct ELWFs.

In Sec. II we also introduce the basic equations of our approach, relying heavily on earlier work [13]. In Sec. III we calculate the ground state electric polarization and magnetization, and discuss the form they take; in Sec. IV we calculate the linear response in the long-wavelength limit. If the system is assumed to initially possess time-reversal symmetry and its energy bands are isolated, then our results follow the pattern sketched above: The induced free current can be associated with intraband transitions, and the polarization current with interband transitions. Here, of course, we have an explicit expression for the polarization, and can calculate the polarization current by directly taking $\partial P/\partial t$; we can thus construct an expression for $\epsilon^{ij}(\omega)$ by direct calculation. The result is gauge-invariant, in the sense that it is independent of how the ELWFs are chosen.

The situation is more complicated if initially there is no time-reversal symmetry. We then find that the linearly induced microscopic charge density, $\langle \hat{\rho}(x, \omega) \rangle$, contains a term proportional to $\omega^{-1}$ and thus diverges as $\omega \rightarrow 0$. This result is independent of how one defines quantities such as microscopic polarization and magnetization fields, and free charge and current densities. But it is then not surprising that the $\rho_R^{(1)}(x, \omega)$ also diverge as $\omega \rightarrow 0$, and thus that $P^{(1)}(\omega)$ – associated with the electric dipole moments of those localized charge densities – does as well. Such a result is inevitable in the approach we adopt, where polarization and magnetization are associated with quantities localized about each lattice site; technically, this originates from an “intraband contribution” to $P^{(1)}(\omega)$ that is non-vanishing only if time-reversal symmetry is broken in the unperturbed crystal. This intraband contribution to $P^{(1)}(\omega)$ is divergent and leads to a finite contribution to the induced macroscopic current density $-i\omega P^{(1)}(\omega)$ as $\omega \rightarrow 0$. In addition to a contribution to $J_E^{(1)}(\omega)$ that is divergent as $\omega \rightarrow 0$, and arises as an expected generalization of (2), we also find a contribution that is finite as $\omega \rightarrow 0$. When this is combined with the finite contribution to $-i\omega P^{(1)}(\omega)$ as $\omega \rightarrow 0$ we find a gauge-invariant contribution to $J_E^{(1)}(\omega)$ that is finite as $\omega \rightarrow 0$, and can be identified as giving rise to the anomalous Hall current. The other contributions to $J^{(1)}(\omega)$, which are also gauge-invariant, correspond to the generalization of (2) and to a pure interband response of $P^{(1)}(\omega)$. Here we can also introduce an $\epsilon^{il}(\omega)$, but it is perhaps more natural to write

$$J^{(1)}(\omega) = \sigma^{il}(\omega)E_l(\omega),$$

where $\sigma^{il}(\omega) = -i\omega(\epsilon^{il}(\omega) - \delta^{il}/(4\pi))$, and at the end of Sec. IV we give the general expression for $\sigma^{il}(\omega)$.

Our conclusions and perspectives on future work are presented in Sec. V.

II. SINGLE-PARTICLE DENSITY MATRIX

We will consider a simple instance of a metallic system, a p-doped semiconductor, perturbed by a uniform electric field. We restrict our study to 2- and 3-dimensional crystalline solids, and implement the frozen-ion and independent-particle approximations. Thus, the only dynamical degrees of freedom of the crystal are electronic and, in the Heisenberg picture, we take that dynamics to be captured by the electron field operator, $\psi_0(x, t)$.

In the unperturbed crystal, $\psi_0(x, t)$ evolves according $i\hbar \frac{d}{dt} \psi_0(x, t) = [\psi_0(x, t), H_0]$, for one-body Hamiltonian...
operator \( \hat{H}_0 = \int \psi^\dagger_0(x,t)H_0(x,p(x))\psi_0(x,t)dx \), where

\[
H_0(x,p(x)) = \frac{(p(x))^2}{2m} + V(x), \tag{5}
\]

with \( V(x) = V(x + R) \) for any Bravais lattice vector \( R \) of the crystalline solid of interest being the cell-periodic potential accounting for the electromagnetic interaction of the electron field with the fixed ion cores, and

\[
p(x) \equiv \frac{\hbar}{i} \nabla - \frac{e}{c} A_{\text{static}}(x) \tag{6}
\]

being associated with the “physical momentum” of the unperturbed crystal; we allow for the presence of an “internal”, static, cell-periodic magnetic field described by the vector potential \( A_{\text{static}}(x) \), where \( A_{\text{static}}(x) = A_{\text{static}}(x + R) \), and consequently (5) generally breaks time-reversal symmetry. We assume that the set of energy eigenvalues \( E_{nk} \) of the cell-periodic Hamiltonian (5) admits a band gap, below which we take the Fermi energy \( E_F \) to lie (see Fig. 1). Thus, a distinction can be made between the set of electronic eigenvectors that are associated with partly occupied energy bands and those that are associated with completely unoccupied energy bands in the zero temperature electronic ground state, which we take to be the initial state of the crystal.

In recent times, it has become clear that the spectral data of the relevant Hamiltonian does not completely characterize a system and that some topological data must also be identified. In addition to this matter of principle, the implementation of ELWFs is crucial in the formalism we employ, as described in Sec. I, and the existence of a set of such ELWFs is intimately related to this topological data. Technically, the existence of a complete set of ELWFs [26] is equivalent to the existence of a global smooth frame of the Hilbert bundle over the Brillouin zone torus constructed using the eigenvectors associated with all of the energy bands, which we term the Bloch bundle [27]. The components of such a frame, which at each \( k \in \text{BZ} \) is a basis of the Hilbert space spanned by all of the electronic energy eigenvectors, or equivalently their cell-periodic analogue, identified by that \( k \), and that is smooth over BZ, can generally be written [22, 28, 29]

\[
|\alpha k\rangle = \sum_n U_{n\alpha}(k) |nk\rangle, \tag{7}
\]

where \( u_{nk}(x) \equiv \langle x|nk\rangle \equiv (2\pi)^{d/2} e^{-ik\cdot x} \langle x|\psi_{nk}\rangle \) are cell-periodic functions normalized over the unit cell that are related to the electronic energy eigenvectors \( |\psi_{nk}\rangle \); in what follows, sums are generally taken over all band indices \( n \) or all type indices \( \alpha \) unless otherwise indicated. It is then each of the vectors \( |\alpha k\rangle \), which are smooth over the Brillouin zone, that can be mapped to an ELWF \( |\alpha R\rangle \) via the (inverse) Bloch-Floquet-Zak transform [23, 30],

\[
\langle x|\alpha R\rangle = \sqrt{|\Omega_{uc}|} \int_{\text{BZ}} d^d k  e^{i \cdot (x-R)} \langle x|\alpha k\rangle, \tag{8}
\]

where the ELWFs are identified by a “type index” \( \alpha \) and the Bravais lattice vector \( R \) with which it is associated. Additionally, the existence of such a global smooth frame is equivalent to the existence of a global trivialization of the Bloch bundle [31]; remarkably, it has been shown that the latter exists in general [32]. This implies the vanishing of any Chern numbers that characterize the Bloch bundle [33]; this is often understood implicitly in the physics literature [34]. Generally, the construction outlined above corresponds to using \textit{all} of the electronic

\[
\left\{ |n\rangle \mid n \in \{N+1, N+2, \ldots\} \right\} \quad \rightarrow \quad \left\{ |\alpha k\rangle \mid \alpha \in \{N+1, N+2, \ldots\} \right\}
\]

\[
\left\{ |n\rangle \mid n \in \{1, 2, \ldots, N\} \right\} \quad \rightarrow \quad \left\{ |\alpha k\rangle \mid \alpha \in \{1, 2, \ldots, N\} \right\}
\]

FIG. 1: Schematic of the energy bands whose associated eigenvectors would be used in the construction of ELWFs in a hypothetical \( d > 1 \) crystalline solid (the bandstructure of GaAs, which we import from a past publication [25], is used only for illustrative purposes). Upper (red) and lower (blue) horizontal dashed lines indicate possible Fermi energies for a trivial insulator and for a doped semiconductor, respectively.
energy eigenvectors to construct a complete set of ELWFs; in general, the matrix \( U(k) \) has no nonvanishing entries. However, often times, and as we will take to be the case in this paper, a number of Hilbert subbundles of the Bloch bundle are trivializable, in which case a subset of the complete set of ELWFs can be constructed from a subset of all the electronic energy eigenvectors.

We here restrict our study to crystals for which the Hilbert bundle associated with any set of isolated energy bands is globally trivializable. Thus, if the Fermi energy is taken to coincide with the lower (blue) dashed line of Fig. 1, then there are initially \( N \) partly occupied energy bands that are isolated from the completely unoccupied bands and \( U(k) \) will take block diagonal form, with the “upper left” block being \( N \) bands that are isolated from the completely unoccupied bands is globally trivializable. Thus, if the Fermi energy Hilbert bundle associated with \( U(k) \), including the \( W^a(k) \) defined below. If the Fermi energy is taken to coincide with the upper (red) dashed line of Fig. 1, then the valence bundle – for a band insulator, this is the Hilbert bundle over BZ with fiber at each \( k \in \text{BZ} \) being the Hilbert space spanned by the occupied energy eigenvectors identified with that \( k \) in the zero temperature ground state – is taken to be globally trivializable and we will classify this as a “trivial” insulator [35].

Such considerations generally apply to any crystalline solid whose spectrum has a band gap; the positioning of the Fermi energy, whether the material is a band insulator or it is metallic, is not immediately relevant. A more general approach to generate such smooth frames in metallic systems where it is not necessary to have isolated sets of energy bands has been formulated [36], and in future work we will implement this construction. However, even within the scheme we implement, an important distinction between metals and trivial insulators arises: For a trivial insulator with \( N \) occupied energy bands there exists a global smooth frame of the valence bundle with components \(|\alpha k\rangle\) labelled by integers \(\alpha \in \{1, 2, \ldots, N\} \) that satisfies \(\forall k \in \text{BZ} : \text{span}_\mathbb{C}(\{|\alpha k\rangle | E_{nk} < E_F \}) = \text{span}_\mathbb{C}(\{|\alpha k\rangle | \alpha \in \{1, 2, \ldots, N\}\})\), while for metals with \( N \) partly occupied bands there exists only such a frame that satisfies \(\forall k \in \text{BZ} : \text{span}_\mathbb{C}(\{|\alpha k\rangle | E_{nk} < E_F \}) \subseteq \text{span}_\mathbb{C}(\{|\alpha k\rangle | \alpha \in \{1, 2, \ldots, N\}\}) \) [28, 36]. This is related to the fact that for metallic systems the bundle over BZ whose fiber at each \( k \in \text{BZ} \) is the Hilbert space spanned by the occupied eigenvectors at that \( k \) is not itself a vector bundle, and thus the notion of a global smooth frame is not well-defined. Instead, one can construct a vector bundle whose fiber at each \( k \) contains, as a subspace, the occupied Hilbert space for that \( k \), which yields the subset relation. Then, while for trivial insulators the subspace \(\text{span}_\mathbb{C}(\{|\alpha k\rangle | \alpha \in \{1, 2, \ldots, N\}\})\) contains only “ground state data”, this is not so for metals. This does not pose an issue since we do not assert that the electronic polarization and magnetization fields involve only the initially occupied energy eigenvectors. Rather, we introduce \( p^\dagger(x, t) \) and \( m(x, t) \) using any set of functions that are sufficiently localized spatially – ELWFs are the most natural and convenient choice – and, by construction, from those fields the ground state expectation values of the charge and current density operators can be found [13].

As illustrated above, deep topological notions underlie the existence of ELWFs, and with this understanding the appearance of related geometric objects in many identities involving ELWFs is less opaque than it might otherwise be. One such identity that will be useful in this work is [28]

\[
\int W^a_{\beta \gamma}(x) x^a W_{\alpha 0}(x) dx = \frac{\Omega_{ac}}{(2\pi)^d} \int_{\text{BZ}} dke^{ik \cdot R} \tilde{\xi}^a_{\beta \gamma}(k),
\]

where \(\Omega_{ac}\) is the volume of the real space unit cell and

\[
\tilde{\xi}^a_{\beta \gamma}(k) = \frac{i}{\Omega_{ac}} \int_{\text{BZ}} u^a_{\beta k}(x) \frac{\partial u_{\alpha k}(x)}{\partial k^a} dx = i(\beta k)\partial_\alpha u_{\alpha k} \tag{9}
\]

are components of the non-Abelian Berry connection that are induced by a global smooth frame with components \(|\alpha k\rangle\). Here \( u_{\alpha k}(x) = \langle x | \alpha k \rangle \) and we adopt the shorthand \( \partial_\alpha = \partial / \partial k^\alpha \). Due to the compatibility of Yang-Mills fields obtained from a given connection 1-form, the components \(\tilde{\xi}^a_{\beta \gamma}(k)\) are related to those components that are induced by a local smooth frame with components \(|\alpha k\rangle\),

\[
\xi^a_{mn}(k) \equiv i(mk)\partial_\alpha u_{\alpha n}, \tag{10}
\]

via the gauge transformation

\[
\sum_{\alpha \beta} U_{m\beta}(k) \tilde{\xi}^a_{\beta \alpha}(k) U^\dagger_{\alpha n}(k) = \xi^a_{mn}(k) + \mathcal{W}^a_{mn}(k). \tag{11}
\]

Here we have defined the Hermitian matrix \(\mathcal{W}^a_{mn}(k)\) populated by elements

\[
\mathcal{W}^a_{mn}(k) \equiv i \sum_{\alpha} (\partial_\alpha U_{m\alpha}(k)) U^\dagger_{\alpha n}(k). \tag{12}
\]

As an abstract mathematical object, the value a given \(\mathcal{W}^a_{mn}(k)\) takes is not manifestly related to the ground state occupation of either of the band indices \(m\) and \(n\); in this paper we will use \(f_{nk}\) to denote the usual Fermi filling factor that is taken to equal 1 (0) if the corresponding energy \(E_{nk}\) is less (greater) than the Fermi energy and in the instance of a band insulator this would be independent of \(k\). However, as we have assumed above and as is often the case in practice, the \(U(k)\) matrix takes a block diagonal form, as discussed after (8). For example, for a trivial insulator ELWFs can be constructed from the occupied energy eigenvectors alone. If this were the case, \(\mathcal{W}^a_{mn}(k) \neq 0\) only if \(f_{nk} = f_n\), which follows from noting that if \(f_{mk} \neq f_m\) then the values of \(m\) for which \(U_{m\alpha}(k) \neq 0\) differ from the values of \(m\) for which \(U_{m\alpha}(k) \neq 0\). In contrast, by definition the valence bundle of a Chern insulator is characterized a non-vanishing first Chern number; thus, that bundle is not globally trivializable and ELWFs cannot be constructed from the occupied energy eigenvectors alone. In this case, \(\mathcal{W}^a_{mn}(k) \neq 0\) in general, even
if \( f_m \neq f_n \). Similar to that case, for the doped semiconductors of interest here, \( W_m^{\alpha\alpha}(k) \neq 0 \) even if \( f_{mk} \neq f_{nk} \); this is related to the discussion in the paragraphs following (8). In addition, under a periodic gauge choice, all objects appearing in (11) are periodic over the Brillouin zone. In what follows, the \( k \)-dependence of the preceding objects is usually kept implicit.

We account for the interaction between the electron field, which is taken to be the only dynamical degree of freedom of the crystal, and the “applied” electromagnetic field via the usual minimal coupling prescription (see Appendix A). From the resulting minimal coupling Hamiltonian, the field-theoretic electronic charge and current operators generating ELWFs and those generating energy eigenvectors to be

\[
\hat{a}_{\alpha\mathbf{R}}(t) = \sqrt{\frac{\Omega_{uc}}{(2\pi)^d}} \int_{\text{BZ}} d\mathbf{k} e^{-i\mathbf{k}\cdot\mathbf{R}} \sum_n U_{\alpha \alpha n} \hat{a}_{\alpha n}(t),
\]

which we implement along with the initial state of the crystalline solid, here taken to be the zero temperature density matrix, and this quantity is sensitive to the initial state of the unperturbed crystal. The definition of the single-particle density matrix involves the fermionic operators \( \hat{a}_{nk} \) and \( \hat{a}_{nk}^\dagger \), which generate the electronic eigenvectors of the unperturbed Hamiltonian \( \hat{H}_0 \); that is, \( |\psi_{nk}\rangle = \hat{a}_{nk}^\dagger |\text{vac}\rangle \) and \( \hat{H}_0 |\psi_{nk}\rangle = E_{nk} |\psi_{nk}\rangle \). Working in the Heisenberg picture, these operators evolve as \( i\hbar \frac{d}{dt} \hat{a}_{nk}(t) = [\hat{a}_{nk}(t), \hat{H}(t)] \), where \( \hat{H}(t) \) involves the classical Maxwell electric field via minimal coupling (see Appendix A). Via (7,8) we find the relation between the operators generating ELWFs and those generating energy eigenvectors to be

\[
\eta_{\alpha\mathbf{R}';\beta\mathbf{R}}(t) = \eta_{\alpha\mathbf{R}';\beta\mathbf{R}}^{(0)} + \eta_{\alpha\mathbf{R}';\beta\mathbf{R}}^{(1)}(t) + \ldots,
\]

where the superscript (0) denotes the contribution to (16) that is independent of \( E(t) \), the superscript (1) denotes the contribution to (16) that is linear in the electric field, and “…” denotes the non-linear contributions. In what follows the latter will be neglected.

In Appendix A we show

\[
\eta_{\alpha\mathbf{R}';\beta\mathbf{R}}^{(0)}(t) = \Omega_{uc} \int_{\text{BZ}} \frac{d\mathbf{k}}{(2\pi)^d} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \sum_n f_{nk} U_{\alpha n} U_{\beta n},
\]

and implementing the usual Fourier series analysis,

\[
g(t) = \sum_\omega e^{-i\omega t} g(\omega),
\]

we also show that the first-order perturbative modification to (16) due to \( E(\omega) \) is

\[
\eta_{\alpha\mathbf{R}';\beta\mathbf{R}}^{(1)}(\omega) = eE(\omega)\Omega_{uc} \int_{\text{BZ}} \frac{d\mathbf{k}}{(2\pi)^d} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \sum_{mn} f_{nm,k} U_{\alpha mn}^\dagger U_{\beta mn} \frac{1}{E_{nk} - E_{mk} - \hbar(\omega + i0^+)} + i\frac{E(\omega)}{\hbar(\omega + i0^+)} \Omega_{uc} \int_{\text{BZ}} \frac{d\mathbf{k}}{(2\pi)^d} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \sum_n (\partial_t f_{nk}) U_{\alpha n}^\dagger U_{\beta n},
\]

\[
\eta_{\alpha\mathbf{R}';\beta\mathbf{R}}(\omega) = eE(\omega)\Omega_{uc} \int_{\text{BZ}} \frac{d\mathbf{k}}{(2\pi)^d} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \sum_{mn} f_{nm,k} U_{\alpha mn}^\dagger U_{\beta mn} \frac{1}{E_{nk} - E_{mk} - \hbar(\omega + i0^+)} + i\frac{E(\omega)}{\hbar(\omega + i0^+)} \Omega_{uc} \int_{\text{BZ}} \frac{d\mathbf{k}}{(2\pi)^d} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \sum_n (\partial_t f_{nk}) U_{\alpha n}^\dagger U_{\beta n},
\]
where $f_{nm,k} \equiv f_{nk} - f_{mk}$. The first term of (19) is the trivial generalization of the previously found perturbative modification for trivial insulators, and can be understood in the context of time-dependent perturbation theory as arising from the interaction term [39]

$$-eE^a(t) \int_{BZ} dk \sum_{n \neq m} \hat{a}^+_{nk}(t) \xi_{nm}^a(k) \hat{a}_{mk}(t). \quad (20)$$

Due to the form of this interaction term we will later describe any first-order modifications that involve the first term of (19) as being “interband”. The second term of (19) is a new contribution, here related to the presence of a Fermi surface. Notably this term diverges in the dc limit, and indeed it is this term that will lead to the expected dc divergence of the induced free current density, as we later show. This term can here be understood as arising from the interaction term

$$-eE^a(t) \int_{BZ} dk \sum_{n} \left( \hat{a}^+_{nk}(t) \xi_{nm}^a(k) \hat{a}_{nk}(t) + \frac{i}{2} \hat{a}^+_{nk}(t) (\hat{\partial}_a \hat{a}_{nk}(t)) - \frac{i}{2} (\hat{\partial}_a \hat{a}^+_{nk}(t)) \hat{a}_{nk}(t) \right). \quad (21)$$

The first term of (21) gives a vanishing contribution to $\eta_{0}^{(1)}_{\alpha \beta} \left( \omega \right)$ for both metals and trivial insulators initially occupying their zero temperature electronic ground state. In contrast, although the second and third terms of (21) as well give vanishing contributions to $\eta_{0}^{(1)}_{\alpha \beta} \left( \omega \right)$ for such trivial insulators, they give rise to finite contributions if the crystal is metallic; these finite contributions involve only the states with energies “near” the Fermi energy (see Appendix A). Due to the form of this interaction term we will later describe the first-order modifications that involve the second term of (19) as being “intraband”. Such an identification of interaction terms that give rise to inter- and intraband contributions at linear response is implicit in the earlier works of Blount [40] and others [41]. The primary difference between our approach and those is that this investigation is a limiting case of a more general framework within which spatial and temporal variation of electric and magnetic fields can be taken into account; that is not the case in earlier works.

The limit of a trivial insulator can be reached from (17) by taking $f_{nk} \to f_n$ and requiring each $|\alpha k\rangle$ to be an element of either the initially occupied or unoccupied Hilbert subspace; the second condition implies that, in general, $\mathcal{W}_{nm}^\alpha(k) \neq 0$ only if $f_n = f_m$ (see discussion below (12)). In this limit, one can define an analogous filling factor $f_\alpha$ associated with $|\alpha k\rangle$; we set the $f_\alpha$ associated with $|\alpha k\rangle$ to equal the $f_n$ associated with the $\{n k\}$ used in its construction. The sum over $n$ in (17) then corresponds to the matrix multiplication of $U(k)$ and its inverse, giving the unit matrix, which in components is $\delta_{\alpha \beta}$. It then follows that, in this limit,

$$\eta_{f\alpha R':\beta R'}^{(0)\text{insulator}} = f_\alpha \delta_{\alpha \beta} \delta_{R' R'},$$

as expected [13]. Implementing this limit in (19) we find

$$\eta_{f\alpha R':\beta R'}^{(1)\text{insulator}} \left( \omega \right) = eE^1(\omega)\Omega_{uc} \int_{BZ} \frac{dk}{(2\pi)^d} e^{i k \cdot (R' - R')} \times \sum_{mn} \frac{f_{nm} U_{\alpha m} U_{\beta n}}{E_{nk} - E_{mk} - \hbar (\omega + i0^+)},$$

again, as expected [13].

### III. unperturbed dipole moments

Although the presence of an electric field breaks the discrete translational symmetry present in the unperturbed system, under the long-wavelength limit implemented in this work some aspects of that symmetry are retained; this is apparent in (19). The “site” polarization and magnetization fields remain physically equivalent in the sense that the electric and magnetic dipole moments associated with each lattice site satisfy

$$\mu_R = \mu_R^e, \quad \nu_R = \nu_{R'},$$

for any Bravais lattice vectors $R$ and $R'$. It follows that the macroscopic polarization and magnetization fields are uniform [20] and can be written as

$$P(t) = \frac{\mu_R(t)}{\Omega_{uc}}, \quad M(t) = \frac{\nu_R(t)}{\Omega_{uc}}, \quad (22)$$

for any $R$. Because we consider the ionic cores within the crystal to be fixed, these charges do not contribute to the magnetization; there will however be a static contribution to the polarization that is found from the “site” polarization fields that are defined from the constituents of a decomposition of $\rho^{xc}(x)$ into “site” contributions [13, 20]. The electric dipole moment associated with lattice site $R$ is defined to be [13]

$$\mu_R^1(t) \equiv \sum_{\alpha \beta R R'} \left( \int (x^i - R^i) \rho_{\beta R'\alpha R'}(x, R; t) dx \right) \eta_{\alpha R' \beta} R'(t) + \left( \mu_R^{\text{mon}} \right)^i,$$  \quad (23)
and the magnetic dipole moment associated with $\mathbf{R}$ to be

$$\nu_R(t) = \frac{1}{2c} \sum_{\alpha \beta} \left( i^{ab} \int (x^a - R^a) \left( j_{\beta R^\prime; \alpha R^\prime} (\mathbf{x}, \mathbf{R}; t) + j_{\beta \mathbf{R}^\prime; \alpha \mathbf{R}^\prime} (\mathbf{x}, \mathbf{R}; t) \right) d\mathbf{x} \right) \eta_{\alpha R^\prime; \beta R^\prime} (t), \tag{24}$$

where $\rho_{\beta R^\prime; \alpha R^\prime} (\mathbf{x}, \mathbf{R}; t)$, $j_{\beta \mathbf{R}^\prime; \alpha \mathbf{R}^\prime} (\mathbf{x}, \mathbf{R}; t)$, and $j_{\beta \mathbf{R}^\prime; \alpha \mathbf{R}^\prime} (\mathbf{x}, \mathbf{R}; t)$ are termed generalized (electronic) “site-quantity matrix elements” and were introduced previously [13]. Again, with the assumption of a valid perturbative expansion (23,24) can be written

$$\mu_R(t) = \mu_R^{(0)} (t) + \mu_R^{(1)} (t) + \ldots,$$

and the same can be done for (22). The first term in each such expansion is identified as the “unperturbed contribution”, and these are the focus of the rest of this section.

### A. Polarization

From (17,23) we find $\mu_R^{(0)}$ to be independent of $\mathbf{R}$, as expected, and the resulting unperturbed polarization is

$$P^{(0)} = e \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} (\xi_{nm} + W_{nm}) + \left( \mu_R^{(0)} \right)_{\eta_{uc}}, \tag{25}$$

which is formally similar to that of a trivial insulator [6, 19], for which $f_{nk} \rightarrow f_n$. As is the case there, apart from a gauge dependent contribution, $P^{(0)}$ vanishes if the unperturbed system is inversion symmetric; as discussed previously [19], we take the gauge dependence of the electronic quantities to be contained entirely within the $U(k)$ and consider any terms that involve this object, including the $V^i(k)$, to be “gauge dependent”. While it appears that the gauge dependent term appearing in (25) no longer generally evaluates to an element of a set of discrete values, at least not following from the same argument that is presented for trivial insulators [6]. $P^{(0)}$ maintains the physically sensible characteristic that upon shifting the origin of all ELWFs by a constant Bravais lattice vector $\mathbf{R}_0$, the polarization is altered by an additive constant that is proportional to that vector. That is, although there is no longer a “quantum of ambiguity” associated with $P^{(0)}$, taking $|\alpha \mathbf{R}_0 \rightarrow |\alpha \mathbf{R}_0 + \mathbf{R}_s\rangle$, or equivalently $U_{\alpha \mathbf{R}} \rightarrow e^{-iE_{\mathbf{R}} U_{\alpha \mathbf{R}}} \eta_{\mathbf{R}}$, and thus $W_{nm}^{\alpha} \rightarrow W_{nm}^{\alpha} + \delta_{nm} R_s^{\alpha}$, yields

$$P^{(0)} \rightarrow P^{(0)} + eN_{el} \mathbf{R}_s,$$

where $N_{el} = \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk}$. We do note however that an expression formally similar to (25) arises in the case of a Chern insulator [42], and while in that case the gauge dependent contribution again would not be discretely valued by the original argument of Resta [6], it indeed has this property when treated carefully [43]. It may therefore be the case that the gauge dependent contribution to (25) always evaluates to an element of a set of discrete values, but we postpone such an investigation for a later work. Finally, (25) is manifestly invariant under a translation of the energy zero, as one would expect.

### B. Magnetization

We first identify the “atomic-like” contribution [4, 13] to the unperturbed magnetization, which arises from the term involving $j_{\beta \mathbf{R}; \alpha \mathbf{R}^\prime} (\mathbf{x}, \mathbf{R}; t)$ in (24). We find

$$\tilde{M}^{(0)} = \frac{e}{2mc} \text{Re} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{n} f_{nk} \sum_{\alpha \beta \mathbf{R}} e^{i k \cdot (\mathbf{R} - \mathbf{R}')} U_{\alpha \beta} \left( e^{i a b} \int W_{\beta \mathbf{R}} (y) y^a p_b (y) W_{\alpha \mathbf{R}' - \mathbf{R}} (y) dy \right) U_{\alpha \beta}^\dagger,$$

$$= \frac{e}{2\hbar c} \text{Re} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{n} f_{nk} \epsilon^{i a b} \left( \left( \xi_{nm} + W_{nm} \right) \partial_b E_{nk} + i \sum_m \left( E_{mk} - E_{nk} \right) \xi_{nm}^a s_{mn}^b - i \sum_m \left( E_{mk} - E_{nk} \right) W_{mn}^a s_{mn}^b \right). \tag{26}$$

The “itinerant contribution” [4, 13], which arises from the term involving $j_{\beta \mathbf{R}; \alpha \mathbf{R}^\prime} (\mathbf{x}, \mathbf{R}; t)$ in (24), is found to be

$$\tilde{M}^{(0)} = \frac{e}{2\hbar c} \text{Re} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{n} f_{nk} \epsilon^{i a b} \left( \left( \xi_{nm} + W_{nm} \right) \partial_b E_{nk} + i \sum_m \left( E_{mk} - E_{nk} \right) W_{mn}^a W_{nn}^b + i \sum_m \left( E_{mk} - E_{nk} \right) W_{mn}^a s_{mn}^b \right). \tag{27}$$

Both (26) and (27) reproduce the usual expressions in the trivial insulator limit; that is, taking $f_{nk} \rightarrow f_n$ and $W_{nm}^n (k) \neq 0$ only if $f_n = f_m$, and implementing the definition of the non-Abelian Berry connection $i \partial u_{nk} (x) / \partial k^\alpha = \alpha \mathbf{R}}$.
\[ e \sum_m \xi_{mn}^a(k) u_{mn}(x) \] to find \( (\partial_{\mu}u_{nk}) H_k | \partial_{\mu}u_{nk} = \sum_m E_{mk} \xi_{mn}^a(k) \xi_{mn}^b(k) \), the result of the “modern theory of magnetization” [5] is recovered. Combining (26) and (27) we have

\[ M^{i(0)} = \frac{e}{2\hbar c} \text{Re} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \epsilon^{iab} \left( 2(\xi_{mn}^a + W_{nn}^a) \partial_n E_{nk} + i \sum_m (E_{mk} - E_{nk}) (\xi_{nm}^a \xi_{mn}^b - W_{nm}^a W_{nm}^b) \right) \]

\[ = \frac{e}{2\hbar c} \text{Re} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n e^{iab} \left( 2(\partial_n f_{nk}) (\xi_{mn}^a + W_{nn}^a) E_{nk} + f_{nk} E_{nk} \partial_n \xi_{mn}^b + i f_{nk} \sum_m E_{mk} \xi_{nm}^a \xi_{mn}^b \right. \]

\[ + \left. i E_{nk} \sum_m (f_{nk} - f_{nk}) W_{nm}^a W_{nm}^b \right). \] (28)

Again, in the limit of a trivial insulator the usual expression is recovered [5]; that is,

\[ M^{i(0;\text{insulator})} = \frac{e}{2\hbar c} \text{Re} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n e^{iab} \left( f_{nk} E_{nk} \partial_n \xi_{mn}^b + i f_{nk} \sum_m E_{mk} \xi_{nm}^a \xi_{mn}^b \right). \]

In particular, in that limit (28) is gauge invariant. Moreover, (28) generally vanishes if the unperturbed system is time-reversal symmetric, as expected.

Again considering the effect of shifting the origin of each ELWF by a Bravais lattice vector \( R_i \), we find

\[ M^{i(0)} \rightarrow M^{i(0)} + \frac{e}{\hbar c} \epsilon^{iab} R_i \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \psi_{mn}^a(k), \]

where we have used \( \psi_{mn}^a(k) = \frac{\hbar}{2} \partial_n E_{nk}. \) The term involving \( R_i \) vanishes as the net current in an unperturbed metal occupying its zero temperature ground state is zero; that is,

\[ \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \psi_{mn}^a(k) = 0. \]

Thus, (28) is unaffected by shifting ELWFs, as physically expected. Moreover, it is manifest that (28) is unchanged by a translation of the energy zero.

### IV. FIRST ORDER MODIFICATIONS

We here consider the linearly induced macroscopic charge and current densities, which can be understood to arise from the induced macroscopic polarization and the induced free charge and current densities; in the long-wavelength limit considered here, the induced macroscopic magnetization would be uniform [20] and thus not contribute to (1). Under the frozen-ion approximation that we implement, there are only electronic contributions to such quantities.

#### A. Polarization

We first consider the contribution to (23) that is first order in \( E(\omega) \). Making contact with past work [19, 20], we mention that the \( \rho_{\beta R^i} \partial_{\alpha R^i}(x, R; \omega) \) do not involve the electric field and so the only contribution to \( \mu_{R^1}^{(1)}(\omega) \) is \( \text{“dynamical”} \), arising from the modification of the single-particle density matrix due to \( E(\omega) \); this is the same as the situation for insulators. Implementing (19) we find

\[ P^{i(1)}(\omega) = e^2 E(\omega) \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{mn} f_{nm} \epsilon_{mn}^{i} (\xi_{mn}^a + W_{nn}^a) + \sum_e \frac{e^2}{\hbar(\omega + i0^+)} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \partial_n (\xi_{mn}^a + W_{mn}^a). \] (29)

This expression has two notable features; it is gauge dependent, and it diverges in the dc limit. The gauge dependence is not troubling because induced free charges and currents are also involved here; ultimately it is only the net induced charge and current densities that need be gauge invariant. Also, in the limit of a trivial insulator the second term vanishes and the expected result is recovered [44]. It is notable however that the distinct terms of (29) are sensitive to different aspects of the gauge transformation; the first term, the interband term, involves only off-diagonal elements of \( W^{i}(k) \), while the second term, the intraband term, involves only diagonal elements. This is to be expected because of the way in which the Lie algebra components of the Berry connection appear. Second, it is notable that a diverging linearly induced polarization in the dc limit is not unprecedented. For example, if one considers a hydrogen atom initially occupying its 2s state, dc divergences occur as a result of non-vanishing matrix elements between 2s and 2p states facilitated by an electric dipole interaction term. Such a divergence could arise from the first term of (29), but does not occur here as we take the crystal to initially occupy its unique electronic ground state, in contrast to this example for the hydrogen atom. Although such a divergence is not entirely novel in principle, the mechanism underlying the divergence of (29) is distinct from that of atomic and molecular physics. We return to this issue in Sec. V.
B. Macroscopic bound and free currents

Like the macroscopic polarization and magnetization, the spatial uniformity of the electric field renders the macroscopic bound and free current densities uniform [20]. Thus we do not indicate any spatial dependence of such quantities. Moreover, both the macroscopic bound and free current densities can found from any one of the “site quantities” used in their construction [13].

Implementing (29) we find the linearly induced macroscopic bound current density [13, 20],

\[ J_B^{(1)}(\omega) = -i\omega P^{(1)}(\omega). \]  

(30)

This is non-diverging in the \( \omega \to 0 \) limit, as would be expected physically. Furthermore, in Appendix B we show that (30) vanishes in the \( \omega \to 0 \) limit if the unperturbed system is time-reversal symmetric.

We now consider the linearly induced macroscopic free current density. The corresponding microscopic density is defined as [13]

\[ j_F(x, \omega) \equiv \frac{1}{2} \sum_{RR'} s(x; R, R') I(R, R'; \omega). \]  

(31)

From the definitions presented in that past work, we find the first-order modification to the link currents \( I(R, R'; \omega) \) to be of the form

\[ I^{(1)}(R, R'; \omega) = \frac{e}{i\hbar} \sum_{\alpha \lambda} \left( H^{(1)}_{\alpha R', \lambda R'}(\omega) \eta^{(0)}_{\alpha R', \lambda R} - \eta^{(0)}_{\alpha R, \lambda R'} H^{(1)}_{\alpha R', \lambda R}(\omega) \right) \]

\[ + \frac{e}{i\hbar} \sum_{\alpha \lambda} \left( H^{(0)}_{\alpha R, \lambda R'} \eta^{(1)}_{\alpha R', \lambda R}(\omega) - \eta^{(1)}_{\alpha R, \lambda R'} H^{(0)}_{\alpha R', \lambda R}(\omega) \right). \]  

(32)

The first term of the above is referred to as a “compositional” modification, arising due to a dependence of the generalized site quantity matrix elements on the electromagnetic field, and the second a “dynamical” modification [19]. An expression for (32) is given in Appendix C, which can explicitly be shown to satisfy

\[ I^{(1)}(R, R'; \omega) = -I^{(1)}(R', R; \omega), \]

as required, as well as

\[ I^{(1)}(R, R'; \omega) = I^{(1)}(R + R_e, R' + R_e; \omega), \]

and

\[ \sum_{R'} I^{(1)}(R, R'; \omega) = 0, \]

as one would physically expect for a translationally invariant system subject to a uniform electric field. The latter can be understood by noting that the electronic “site charges” evolve according to [13]

\[ \frac{dQ_R(t)}{dt} = \sum_{R'} I(R, R'; t), \]

and in this case we expect there to be no build up of charge at any particular lattice site; we therefore expect \( dQ_R(t)/dt \) to vanish. In fact, from the definition of \( Q_R(t) \) and using (19) it can be show that

\[ Q_R^{(1)}(\omega) = \sum_{\alpha} \eta^{(1)}_{\alpha R; \alpha R}(\omega) = 0. \]

Then, in Appendix C we show

\[ j_F^{(1)}(\omega) = \frac{1}{2} \sum_{R'} (R' - R^0) I^{(1)}(R, R'; \omega) \]

\[ = -\frac{e^2}{h} E^f(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \left( \sum_{n} f_{nk} \partial_{\lambda} (\xi^l_{mn} + \mathcal{W}^l_{mn}) + \sum_{nm} f_{nm,k} \text{Im} \left[ (\xi^l_{nm} + \mathcal{W}^l_{nm}) \mathcal{W}^l_{nm} \right] \right) \]

\[ + i\hbar E^f(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{nm} f_{nm,k} \xi^l_{mn} \mathcal{W}^l_{nm} \left( 1 + \frac{\hbar \omega}{E_{mk} - E_{nk} - \hbar (\omega + i0^+)} \right) \]

\[ + i\hbar E^f(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{n} f_{nk} \partial_{\lambda} E_{nk}, \]  

(33)

where the first term in the second line results from the compositional modification of (32), while the second and third terms from the dynamical modification. Notably \( J_F^{(1)}(\omega) \) diverges in the dc limit, which is as one would physically expect given that we have not accounted for any scattering mechanisms. In fact, it is the third term in the second line of (33) that will lead to the dc divergence of the electrical conductivity tensor; this term involves
the second term of (19). Moreover, \( J_p^{(1)}(\omega) \) is gauge dependent, akin to \( J_B^{(1)}(\omega) \), and it is only through this gauge dependence that (33) involves “interband” contributions. Notably if the energy bands of the crystal are isolated from one another then \( W_{nm}(k) \propto \delta_{nm} \) and consequently the interband contributions to \( J_p^{(1)}(\omega) \) vanish; in this limiting case the induced free current density involves only “intrapband” contributions, which is as one would expect for simple models.

C. Time-reversal symmetry

The general expression (29) that we derive for \( P^{(1)}(\omega) \) has the feature that it contains an intraband contribution and this contribution diverges in the dc limit. From the simple picture of polarization presented in Sec. I, the presence of such a contribution is unexpected. While in general our description thus asserts that this simple picture is not complete, in Appendix B we show that such an intraband contribution vanishes if the unperturbed system is time-reversal symmetric and \( P^{(1)}(\omega) \) takes the more expected form

\[
P^{(1)}(\omega) \equiv e^2 E I(\omega) \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,k} \xi_{nm} \times \xi_{nm} + W_{nm}^i}{E_{mk} - E_{nk} - \hbar(\omega + i\theta^+)},
\]

Here \( \equiv \) will denote an equality that holds in the presence of time-reversal symmetry.

Adopting the approach of (3), we find

\[
\epsilon_{\text{inter}}^{il}(\omega) \equiv 4\pi e^2 \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,k} \xi_{nm} \times \xi_{nm} + W_{nm}^i}{E_{mk} - E_{nk} - \hbar(\omega + i\theta^+)},
\]

which, apart from the gauge dependence, is consistent with the insight from analogies with molecular response and the more simple approaches mentioned in Sec. I. That is, for crystalline solids in which time-reversal symmetry holds, it is only interband contributions that are involved in \( P^{(1)}(\omega) \). However, even in this simple case \( P^{(1)}(\omega) \) and \( \epsilon_{\text{inter}}^{il}(\omega) \) remain gauge dependent, and thus the introduction of ELWFs and the ambiguity in their choice need be involved in any discussion of such quantities. In this case the induced macroscopic free current density (33) reduces to

\[
J_p^{(1)}(\omega) \equiv i e^2 \omega E I(\omega) \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,k} \xi_{nm} \times \xi_{nm}}{E_{mk} - E_{nk} - \hbar(\omega + i\theta^+)} + \frac{e^2}{\hbar} \frac{E I(\omega)}{\hbar(\omega + i\theta^+)} \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{n} f_{nk} \partial_{\omega} E_{nk},
\]

still having both interband and intraband contributions. Notably the interband contribution is gauge dependent and cancels with the gauge dependent term appearing in the induced bound current density \( -i\omega P^{(1)}(\omega) \) and thus the net induced current density is gauge independent, as one would expect. In addition, if the “parabolic band approximation” is implemented, that is, if one takes each energy eigenvalue to be found from \( E_{nk} = \hbar^2 |k|^2/2m \), \( J_p^{(1)}(\omega) \) agrees with (2) after the identification \( m_0 = m \) and \( N = N_{el} \). In fact, we find under the parabolic band approximation that

\[
\epsilon_{\text{eff}}^{il}(\omega) \equiv \delta^{il} + 4\pi e^2 \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,k} \xi_{nm} \times \xi_{nm}}{E_{mk} - E_{nk} - \hbar(\omega + i\theta^+)} - \frac{4\pi e^2 N_{el}}{m\omega(\omega + i\theta^+)} \delta^{il},
\]

or

\[
\sigma^{il}(\omega) \equiv -i e^2 \hbar \omega \int_{BZ} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,k} \xi_{nm} \times \xi_{nm}}{E_{mk} - E_{nk} - \hbar(\omega + i\theta^+)} + \frac{ie^2 N_{el}}{m(\omega + i\theta^+)} \delta^{il}.
\]

In moving from the first to the second line in this expression for \( \sigma^{il}(\omega) \), relations that hold only in the presence of time-reversal symmetry are implemented. However, we will find that this latter form of \( \sigma^{il}(\omega) \) holds even in the absence of time-reversal symmetry. Moreover, in the absence of that symmetry \( P^{(1)}(\omega) \) takes the more complicated form (29), which generally involves intraband contributions. This results in \( P^{(1)}(\omega) \) having a more general gauge dependence and as well \( J_p^{(1)}(\omega) \) having a more general gauge dependence. However, as was the case here, when these more general expressions are combined, for instance when constructing \( \epsilon_{\text{eff}}^{il}(\omega) \) or \( \sigma^{il}(\omega) \), the gauge dependent terms again cancel.
D. Induced macroscopic current density

Returning to the more general investigation, and thus allowing the possible breaking of time-reversal symmetry, we understand the basis, the induced current density arising from this term is unique because, unlike the contribution to the current density that is orthogonal to the applied electric field. Thus, we again find that although (30) and (33) are not individually gauge invariant and thus are not themselves directly physically observable, their sum is. Indeed, combining (30) and (33) we find

\[ J^{(1)}(\omega) = \frac{ie^2}{\hbar} E^i(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{mn} f_{nk} (E_{mk} - E_{nk}) \xi_{nm} \xi_{m}^{i} + \frac{ie^2}{\hbar} E^i(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{n} f_{nk} \partial_{l} \partial_{l} E_{nk}. \]

The first term comes from taking \(-i\omega = (E_{nk} - E_{mk}) + (E_{mk} - E_{nk} - i\omega)\) in the interband contribution of \(\mu^{(1)}_R\) to \(J^{(1)}_B(\omega)\) ((29) to (30)). Then it is only the term that is gauge invariant and explicitly energy dependent in this particular contribution to \(J^{(1)}_B(\omega)\) that is not cancelled with terms appearing in \(J^{(1)}_C(\omega), (33)\). In particular it is part of the first term of (33), which is a compositional modification, that combines with the second term of the contribution of (29) to (30) when we calculate \(J^{(1)}(\omega)\), and ultimately it is the combination of these terms that cancel with the interband contribution of (29) to (30) that does not explicitly depend on energy. The second term arises from the induced free current density alone and is the only term in (33) that does not cancel with terms from (30). While the “origin” of each of the terms can most easily be seen in the above form of the expression, it can be rewritten in a more familiar form,

\[ J^{(1)}(\omega) = -ie^2 \omega E^i(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{mn} f_{nk} (E_{mk} - E_{nk}) \xi_{nm} \xi_{m}^{i} + \xi_{nm} \xi_{m}^{i} \]

In the limit of a trivial insulator, (34) agrees with usual perturbative calculations using the minimal coupling Hamiltonian. Also, the final term is in agreement with traditional calculations [45]. Moreover, this is in agreement with a direct calculation of the linearly induced macroscopic current density via our formalism.

The final term of (34) can be understood as a “Drude” contribution. This term follows from the final term of (19), and enters here via the induced free current density (33). Notably, such a term can lead to an induced current density that is orthogonal to the applied electric field. This is not to be confused with the well-understood anomalous Hall conductivity however, because in this case since the Cartesian components \(i\) and \(l\) are symmetric there exists a basis in which this contribution to the conductivity tensor is diagonal. Physically this means that, were the applied electric field characterized by a single non-vanishing component with respect to such a basis, the induced current density arising from this term would be parallel to that field. Thus, we understand the possibility of such an induced orthogonal current density to be entirely a consequence of crystalline anisotropy.

In contrast, the first and second terms of (34) are related to both the induced bound and free current densities. Notably, the second term can be understood as a finite-frequency generalization of the “anomalous Hall” current density [46]. This portion of the induced current density is unique because, unlike the contribution from final term of (34), the spatial components \(i\) and \(l\) are asymmetric and consequently there does not exist a basis in which this contribution is diagonal; there does not exist a basis in which the induced current associated with this term is parallel to the applied electric field.

E. Microscopic charge and current densities

The divergence of (29) in the dc limit may raise concerns about our identification of the polarization. We are thus motivated to consider the first-order modifications of the expectation values of the electronic charge and current density operators due to \(E(\omega)\) — quantities
that could be found from traditional perturbation theory with the minimal coupling Hamiltonian [47] – with the

\[ \langle \hat{\rho}(\mathbf{x}, \omega) \rangle^{(1)} = e^2 E^i(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,kl}}{E_{mn} - E_{nk} - i(\omega + i\epsilon)} \psi_{n,k}^*(\mathbf{x}) \psi_{m,k}(\mathbf{x}) + ie^2 \frac{E^i(\omega)}{\hbar(\omega + i\epsilon)} \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \partial_l (\psi_{n,k}^* \psi_{n,k}(\mathbf{x})), \]

and

\[ \langle \hat{j}^i(\mathbf{x}, \omega) \rangle^{(1)} = \frac{e^2}{m} E^i(\omega) \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_{mn} \frac{f_{nm,kl}}{E_{mn} - E_{nk} - i(\omega + i\epsilon)} \psi_{n,k}^* \mathbf{p}^i(\mathbf{x}) \psi_{m,k}(\mathbf{x}) + \frac{ie^2}{m} \frac{E^i(\omega)}{\hbar(\omega + i\epsilon)} \int_{\text{BZ}} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \partial_l (\psi_{n,k}^* \mathbf{p}^i(\mathbf{x}) \psi_{n,k}(\mathbf{x})). \]

The electronic charge and current density operators that we implement are those that arise via Noether’s theorem and thus satisfy the continuity equation

\[ \frac{\partial}{\partial t} \rho(\mathbf{x}, t) + \frac{\partial}{\partial x^a} j^a(\mathbf{x}, t) = 0. \]

Assuming an expansion of these operators in powers of the electric field exists, continuity must then hold at each order in \( E(\omega) \). The same must then be true of the expectation values of such operators. This can be shown explicitly to be the case at first order; implementing (35,36), we find

\[ -i\omega \langle \hat{\rho}(\mathbf{x}, \omega) \rangle^{(1)} + \frac{\partial}{\partial x^a} \langle \hat{j}^a(\mathbf{x}, \omega) \rangle^{(1)} = 0, \]

given that in principle charge is conserved in the unperturbed system in a perturbative scheme.

Notably, (35) has a dc divergence taking a form similar to that of (29). Like that second term of (29), the second term of (35) vanishes if the unperturbed system is time-reversal symmetric, although this symmetry does not cause the second term of (36) to vanish. Thus, it appears that if one insists on defining electric multipole moments by way of partitioning the electronic charge density into portions that are used to define “site” polarization fields from which “site” multipole moments are extracted and summed to give the full electric multipole moments of the system, whether that be via the approach we implement here or some other method, it is unavoidable that one will find a such a dc divergence. In a sense, this unexpected dc divergence is not arising as a consequence of our identification of the microscopic polarization field, but rather it is inherent to the induced charge density at low frequencies.

V. CONCLUSION

In this work we have considered how polarization and magnetization fields can be defined for metallic systems. In contrast to the approach of the “modern theories of polarization and magnetization”, we based our approach on a previously developed strategy [13] for defining microscopic polarization and magnetization fields, the macroscopic analogues of which are defined by spatial averaging. Exponentially localized Wannier functions (ELWFs) play a central role in how the electronic contributions to such quantities are defined. In a trivial insulator the macroscopic charge and current densities, \( \rho \) and \( J \), can be obtained from the macroscopic polarization \( P \) and magnetization \( M \) fields alone; for a metal there will also be contributions from the macroscopic free charge and free current densities, \( \varrho_F \) and \( J_F \).

We here implement this formalism for a \( p \)-doped semiconductor, for which we assume the Hilbert bundle over the Brillouin zone torus associated with any set of isolated energy bands is globally trivial. With this, and because we assume the existence of a band gap above the Fermi energy, contact with expressions for a trivial insulator can readily be reached as a limiting case of the more general expressions that we derive. Indeed, in this work we derive expressions for \( P^{(0)} \) and \( M^{(0)} \) considering the crystal to initially occupy its zero temperature metallic ground state prior to any perturbation being applied, and in the limit of vanishing doping these expressions reduced to those of the “modern theories”. While in that limit the expressions for \( P^{(0)} \) is unique modulo a “quantum of ambiguity” and \( M^{(0)} \) is gauge-invariant in the sense that it is independent of how the ELWFs are constructed, this is not so for a metal. Nonetheless the polarization exhibits the sensible characteristic that upon shifting the origin of all ELWFs by a constant Bravais lattice vector the polarization is altered in the expected way; the magneti-
zation is unaffected by such a shift, and both quantities are unchanged by a shift of the zero-point energy.

Although the expressions we derive for the unperturbed, ground state, macroscopic polarization and magnetization agree with the modern theories in the limit of a trivial insulator, the two approaches disagree more generally. In the modern theory of polarization it has been argued that $P^{(0)}$ is not a well-defined quantity in metallic systems [9, 11]. In contrast, via the approach implemented here we derive an expression for $P^{(0)}$ that is formally similar to that of a trivial insulator. The modern theory of magnetization admits a generalization based on thermodynamic arguments to admit an expression for $M^{(0)}$ valid for metals and Chern insulators [11, 12], but even so the expression we derive does not agree. The disagreement of the expressions derived via these differing approaches is not surprising due to the underlying philosophical differences between them; we consider polarization and magnetization to fundamentally arise as microscopic quantities from which macroscopic analogues are derived, while the modern theory views such quantities as being fundamentally macroscopic. The primary difference between the expression for $M^{(0)}$ derived here and that of the modern theory is that we find this quantity to be gauge dependent, while it is there found to involve a chemical potential explicitly, even in the case of a Chern insulator. Ultimately these two approaches should be viewed as distinct from one another, even though they happen to agree in the simple case of a trivial insulator. An advantage of the approach we implement is that the polarization and magnetization are on the same footing in that they are always well-defined for all systems, and moreover expressions for free charge and current densities are identified; by construction, these quantities together satisfy the expressions familiar from electrodynamics.

In Sec. IV we considered the linear response of the metallic system to a perturbing optical field at finite frequency, a more general response than is typically considered in the “modern theories”. We consider the “long-wavelength limit”, within the independent particle and frozen-ion approximations, where the applied electric field is taken to be the Maxwell field. Here only $P$ and $J_F$ make a contribution to the full macroscopic current density, $J = \partial P / \partial t + J_F$. While in elementary models of the optical response of metals the linearly induced polarization current density is associated with interband response and the linearly induced free current density with the intraband response, here we find a more general scenario. However we do find that if the energy bands are isolated then $J^{(1)}_F$ has only intraband contributions, which is in agreement with those more simple models.

If the unperturbed system exhibits time-reversal symmetry only interband response is relevant to $\partial P^{(1)} / \partial t$, while both interband and interband response contribute to $J^{(1)}_F$. Notably $\partial P^{(1)} / \partial t$ and $J^{(1)}_F$ are both gauge dependent, and it is only via a gauge dependent term that $J_F$ involves the interband response. However, an “effective” dielectric tensor that can be introduced to describe the full optical response, which can be used to relate the full linearly induced macroscopic current density $J^{(1)}_F$ to the applied electric field, is gauge invariant; it contains the expected term that diverges as $\omega^{-1}$ in the absence of scattering mechanisms, the “Drude” contribution.

The situation is more complicated if the unperturbed system violates time-reversal symmetry. Then we find there to be a term in the linearly induced microscopic charge density that diverges as $\omega^{-1}$. This behavior is of course independent of any introduction of polarization and magnetization fields, but in an approach such as ours that relates the macroscopic polarization to electric dipole moments associated with “site” contributions to the microscopic charge density, the result is an induced macroscopic polarization that diverges as $\omega^{-1}$. This term in $P^{(1)}$ appears as a consequence of the intraband response and, when implemented in constructing the full $J^{(1)}_F$, this term combines with a “compositional” modification to the induced free current density to cancel with a contribution to the induced polarization current density related to the interband response. The resultant response tensor is gauge invariant and reproduces the accepted conductivity tensor of a metal, including the “anomalous Hall” contribution.

It is interesting to note that it is the same mechanism that gives rise to the dc divergences of both $P^{(1)}(\omega)$ and $J^{(1)}_F(\omega)$. Both divergences involve the second term of (19), which we show in Appendix A is a consequence of an interaction term that gives rise to the “intraband response”; in this way of identifying inter- and intraband contributions to the linear response we can make contact with earlier work by Blount and others, although the formalism in which we work is indeed much more general. Moreover, the dc divergences of both $P^{(1)}(\omega)$ and $J^{(1)}_F(\omega)$ are here related to the existence of a Fermi surface; for trivial insulators the contribution from this interaction term vanishes in the linear response of the single-particle density matrix. However, even in the case of a trivial insulator, the involvement of the intraband response in the polarization has been previously acknowledged [44]. In particular this has been illustrated by the relevance of intraband contributions at non-linear response. Here we see that, even at linear response, such intraband contributions play a fundamental role in the response of the polarization.

In summary, then, in the approach we have implemented the optical response of the electronic current density to an electric field is gauge invariant. A positive feature of the approach implemented here is that it captures the complete finite-frequency response of a metallic crystal; there is no need to implement distinct approaches to calculate the anomalous Hall and Drude contributions to $J^{(1)}_F$. But the simple association of the free current density $J^{(1)}_F$ with intraband response and the polarization current density $\partial P^{(1)} / \partial t$ with interband response does not hold; in general there are inter- and intraband contributions to both, and both are gauge dependent. One
could argue that this feature, as well as the result that if the unperturbed system violates time-reversal symmetry there is a divergent contribution to the response of the polarization to the electric field, suggests that a different definition of polarization would be more appropriate. However, this would require a significantly different viewpoint than the one we implement here, and indeed such a purported new polarization could not be associated with the dipole moment of microscopic charge densities localized about individual lattice sites.

Of course, a more general argument could be made against the philosophy of our investigations. Our goal, a critic might assert, should be to seek what could be taken as “unique” definitions of \( P, M, \varrho_F, \) and \( J_F, \) and in fact for a metal we do not even demonstrate that for \( P \) and \( M \) in the ground state. We would reply that such uniqueness is not a reasonable goal. After all, even in the ground state of a trivial insulator the value of the polarization is subject to a “quantum of ambiguity” [6]. And once one moves to a general temporal and spatial dependence there are clearly a host of fields \( P(x,t), M(x,t), \varrho_F(x,t), \) and \( J_F(x,t) \) that could be used to describe the physical quantities \( \varrho(x,t) \) and \( J(x,t) \) according to (1). Indeed, for one such set another can be constructed using any vector fields \( a(x,t) \) and \( C(x,t), \) and any scalar field \( b(x,t), \) according to

\[
\begin{align*}
P'(x,t) &= P(x,t) + \nabla \times a(x,t) + C(x,t), \\
M'(x,t) &= M(x,t) - \frac{\partial a(x,t)}{\partial t} + \nabla b(x,t), \\
\varrho'_F(x,t) &= \varrho_F(x,t) + \nabla \cdot C(x,t), \\
J'_F(x,t) &= J_F(x,t) - \frac{\partial C(x,t)}{\partial t}.
\end{align*}
\]

Our perspective is that the focus should be on exploring what might be useful ways of introducing such quantities, for the purpose of both physical insight and calculation. Within that framework this paper can be taken as one such contribution.

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VII. APPENDICES

Appendix A: Perturbation theory in the long-wavelength limit

Although the expression (19) can be found quickly as an extension of earlier work [13], we believe some insight can be gained by looking at its derivation using a more traditional perturbation theory approach.

Consider first a molecule, where nuclei are considered fixed and the dynamics of the electron field operator \( \psi(x,t) \) follows from the usual minimal coupling Hamiltonian,

\[
\mathcal{H}_{\text{mec}}(x,t) = \frac{1}{2m} \left( \mathbf{p}(x) - \frac{e}{c} \mathbf{A}(x,t) \right)^2 + V(x) + e \phi(x,t),
\]

where \( \mathbf{p}(x) \) is given previously (6), the applied field is described by the scalar and vector potentials \( \phi(x,t) \) and \( \mathbf{A}(x,t) \), and \( V(x) \) is the potential energy that confines the electrons to the nuclei. If the wavelength of light is much larger than the molecule, then the electric field \( \mathbf{E}(x,t) \) can be taken as uniform over the molecule, \( \mathbf{E}(x,t) = \mathbf{E}(t) \), and the magnetic field can be neglected. Via usual strategies [13], it can be shown that the dynamics of the electron field follows from the dipole Hamiltonian

\[
\mathcal{H}_{\text{dip}}(x,t) = \mathcal{H}_0(x,\mathbf{p}(x)) - e \mathbf{x} \cdot \mathbf{E}(t), \quad (A1)
\]

where \( \mathcal{H}_0(x,\mathbf{p}(x)) = \frac{\hbar}{2m} (\mathbf{p}(x))^2 + V(x) \).

The use of (A1) to describe instead the response of the electrons in an infinite crystal to long-wavelength radiation, where \( \mathcal{H}_0(x) \) is now taken to be the Bloch Hamiltonian, is a strategy followed by Blount and others [40]; it has even been used to describe the nonlinear optical response of metals [48]. The appearance of a position operator in the interaction Hamiltonian requires calculations to be done cautiously, for giving meaning to matrix elements of the position with respect to the Bloch functions of the infinite crystal in a careful way is obviously problematic. In fact, the usual position operator is generally ill-defined to act on the Hilbert space containing such Bloch functions [9]. Moreover, it does not seem possible to implement a generalization of this kind of approach to treat instances where the electromagnetic field cannot be treated as uniform. Indeed, that is one of the reasons the approach applied in this paper was developed. Nonetheless, this strategy does allow for the interaction Hamiltonian to be written as the sum of two terms, which can be identified as “interband” and “intra-band”. This permits the identification of the interband and intraband contributions to (19), at least within this perspective, and allows us to make contact with earlier work. And so we here present a derivation of (19) using this approach. Although most derivations [40] work with Bloch functions from the onset, some issues related to the position operator can be avoided if one works, at least initially, in the Hilbert space containing ELWFs, the space of square-integrable functions, where the usual position operator is well-defined. This is the approach we follow here. Moreover, we believe that this approach elucidates the physics of the two terms. Yet we ask the reader to forgive the mathematically questionable steps that are part of the derivation and that are not characteristic of the rest of this paper. We feel that the cavalier approach
we take in this Appendix is justified by the insight that the resulting expression gives. The one-body operator related to (A1) is
\[ \hat{H}(t) = \hat{H}_0(t) + \hat{V}_{\text{dip}}(t), \] (A2)
where
\[ \hat{H}_0(t) = \int \hat{\psi}_i^\dagger(x, t) H_0(x, p(x)) \hat{\psi}(x, t) dx, \]
\[ \hat{V}_{\text{dip}}(t) = -\epsilon E^a(t) \int \hat{\psi}_i^\dagger(x, t) x^a \hat{\psi}(x, t) dx. \]
The primary quantities of interest, the expectation values of the electron charge and current density operators for a crystal initially occupying its zero temperature ground state, can be extracted from the single-particle electron Green function,
\[ G(x, y; t) \equiv i \langle \psi(t)| \hat{\psi}_0^\dagger(y, t) \hat{\psi}(x, t) |\psi(t) \rangle. \] (A3)

We now move from the Heisenberg picture to the interaction picture, wherein electronic operators evolve under \[ \hat{H}_0 \] and the effect of the perturbation is accounted for in the evolution of the electronic state \[ |\psi(t)\rangle = \hat{U}(t)|\psi_0\rangle \], where the time-evolution operator \[ \hat{U}(t) \] is given by [49]
\[ \hat{U}(t) = 1 + \sum_{N=1}^\infty \int_{-\infty}^t \frac{dt_N}{\hbar} \hat{V}_1(t_N) \cdots \int_{-\infty}^t \frac{dt_1}{\hbar} \hat{V}_1(t_1), \] (A4)
and where \[ \hat{V}_1(t) \equiv -eE^a(t) \int \hat{\psi}_0^\dagger(x, t) x^a \hat{\psi}_0(x, t) dx. \] The electron Green function (A3) is then rewritten as
\[ G(x, y; t) = i \langle \psi(t)| \hat{\psi}_0^\dagger(y, t) \hat{\psi}_0(x, t) |\psi(t) \rangle. \] (A5)
Noting that a set of exponentially localized Wannier functions span the single-particle electronic Hilbert space, the related operators can be used as a basis with respect to which the electronic field operator can be expanded,
\[ \hat{\psi}_0(x, t) = \sum_{\alpha R} W_{\alpha R}(x) \hat{a}_{\alpha R}(t), \] (A6)
where the operator \[ \hat{a}_{\alpha R}(t) \] here evolves as
\[ i\hbar \frac{d}{dt} \hat{a}_{\alpha R}(t) = [\hat{a}_{\alpha R}(t), \hat{H}_0] \]
and thus \[ \hat{a}_{\alpha R}(t) = e^{i\hat{H}_0 t/\hbar} \hat{a}_{\alpha R} e^{-i\hat{H}_0 t/\hbar}. \] We then have
\[ \hat{V}_1(t) = -\epsilon \frac{\Omega_{\alpha c}^a}{(2\pi)^d} E^a(t) \sum_{\alpha R R'} \left( \int_{\text{BZ}} d\mathbf{k} e^{i\mathbf{k} \cdot (\mathbf{R} - \mathbf{R}')} \tilde{c}_\alpha^a(k) \right) \hat{a}_{\alpha R}(t) \hat{a}_{\alpha R'}(t) - e E^a(t) \sum_{\alpha R} \hat{R}_a^a \hat{a}_{\alpha R}(t) \hat{a}_{\alpha R}(t). \] (A7)
Implementing this into (A4) and using the result in (A5), we find
\[ G(x, y; t) = i \langle \psi(t)| \hat{\psi}_0^\dagger(y, t) \hat{\psi}_0(x, t) |\psi(t) \rangle + \frac{1}{\hbar} \int_{-\infty}^t dt' \langle \psi(t)| \hat{\psi}_0^\dagger(y, t) \hat{V}_1(t') |\psi(t) \rangle |\psi(t) \rangle - \frac{1}{\hbar} \int_{-\infty}^t dt' \langle \psi(t)| \hat{\psi}_0^\dagger(y, t) \hat{\psi}_0(x, t) |\psi(t) \rangle |\psi(t) \rangle + \ldots \]
\[ \equiv i \sum_{\mu R_1; R_2} W_{\mu R_2}(x) \left( \eta_{\mu R_1; \mu R_2}^{(0)} + \eta_{\mu R_1; \mu R_2}^{(1)}(t) + \ldots \right) W_{\mu R_1}^*(y). \] (A8)

Now,
\[ G_0(x, y; t) \equiv i \langle \psi(t)| \hat{\psi}_0^\dagger(y, t) \hat{\psi}_0(x, t) |\psi(t) \rangle = \sum_n \int_{\text{BZ}} d\mathbf{k} f_{nk} \psi_{nk}^*(y) \psi_{nk}(x) \]
\[ = \sum_{\mu \nu R_1 R_2} W_{\nu R_2}(x) \left( i \frac{\Omega_{\mu c}}{(2\pi)^d} \sum_n \int_{\text{BZ}} d\mathbf{k} f_{nk} e^{i\mathbf{k} \cdot (\mathbf{R}_2 - \mathbf{R}_1)} U_{\nu \mu}^*(k) U_{\nu \mu}(k) \right) W_{\mu R_1}^*(y), \]
and we thus identify
\[ \eta_{\nu R_2; \mu R_1}^{(0)} = \frac{\Omega_{\mu c}}{(2\pi)^d} \sum_n \int_{\text{BZ}} d\mathbf{k} f_{nk} e^{i\mathbf{k} \cdot (\mathbf{R}_2 - \mathbf{R}_1)} U_{\nu \mu}^*(k) U_{\nu \mu}(k), \] (A9)
yielding (17).
Next consider \( \eta_{\nu R_2;\mu R_1}(t) \), which from (A8) we identify as

\[
\eta_{\nu R_2;\mu R_1}^{(1)}(t) = \frac{\iota e}{\hbar} \frac{\Omega_{\nu c}}{(2\pi)^d} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha \beta R R'} \int_{BZ} dK e^{iK' \cdot (R' - R)} \tilde{\xi}_{\alpha \beta}^{a}(K') \left( \langle gs | \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) \hat{a}^{\dagger}_{\alpha R}(t') \hat{a}_{\beta R'}(t') | gs \rangle \right)
\]

\[
+ \frac{\iota e}{\hbar} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha R} R^{a} \left( \langle gs | \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) \hat{a}^{\dagger}_{\alpha R}(t') \hat{a}_{\alpha R}(t') | gs \rangle \right)
\]

\[
- \frac{\iota e}{\hbar} \frac{\Omega_{\nu c}}{(2\pi)^d} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha \beta R R'} \int_{BZ} dK e^{iK' \cdot (R' - R)} \tilde{\xi}_{\beta \alpha}^{a}(K') \left( \langle gs | \hat{a}^{\dagger}_{\beta R'}(t') \hat{a}_{\alpha R}(t') \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) | gs \rangle \right)
\]

\[
- \frac{\iota e}{\hbar} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha R} R^{a} \left( \langle gs | \hat{a}^{\dagger}_{\alpha R}(t') \hat{a}_{\alpha R}(t') \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) | gs \rangle \right)
\]

\[
\equiv \eta_{\nu R_2;\mu R_1}^{(1a)}(t) + \eta_{\nu R_2;\mu R_1}^{(1b)}(t).
\]

(A10)

We group the second and final lines of \( \eta_{\nu R_2;\mu R_1}^{(1)}(t) \) into \( \eta_{\nu R_2;\mu R_1}^{(1a)}(t) \), and the first and third lines into \( \eta_{\nu R_2;\mu R_1}^{(1b)}(t) \).

That is, \( \eta_{\nu R_2;\mu R_1}(t) \) involves the contributions to \( \eta_{\nu R_2;\mu R_1}^{(1)}(t) \) arising from the first term of (A7), while \( \eta_{\nu R_2;\mu R_1}^{(1b)}(t) \) involves the contributions to \( \eta_{\nu R_2;\mu R_1}^{(1)}(t) \) arising from the second term of (A7). After some algebra we find

\[
\eta_{\nu R_2;\mu R_1}^{(1a)}(t)
\]

\[
= \frac{\iota e}{\hbar} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha R} R^{a} \left( \langle gs | \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) \hat{a}^{\dagger}_{\alpha R}(t') \hat{a}_{\alpha R}(t') | gs \rangle - \langle gs | \hat{a}^{\dagger}_{\alpha R}(t') \hat{a}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) | gs \rangle \right)
\]

\[
= \epsilon \sum_{\omega} e^{-i(\omega + i0^{+})t} E^{\alpha}(\omega) \Omega_{\nu c} \sum_{n} \int_{BZ} dk \left( f_{n,k} e^{iK' \cdot (R_2 - R_1)} \frac{(R_2^a - R_1^a)U^{\dagger}_{vn}(k)U_{nm}(k) + i\partial_{v}(U^{\dagger}_{vn}(k)U_{nm}(k))}{\hbar(\omega + i0^{+})} \right)
\]

\[
- \sum_{m} \frac{f_{nm,k} e^{iK' \cdot (R_2 - R_1)}}{E_{mk} - E_{nk} - \hbar(\omega + i0^{+})} W_{mn}^a(k)U_{nm}(k)
\]

(A11)

where we have integrated by parts and taken any surface terms to vanish; this vanishing is either due to the periodicity of the integrands over the BZ if considering completely filled energy bands, or alternatively using the fact that \( f_{n,k} \) vanish at the Brillouin zone boundary for a partly occupied band. We have also taken the electric field \( E(t) \) to be adiabatically applied at \( t = -\infty \) resulting in the “0+” in the denominator. We now consider \( \eta_{\nu R_2;\mu R_1}^{(1b)}(t) \). Using the completeness relation of the electronic Fock space

\[
1 = |gs\rangle \langle gs| + \sum_{cv} \int_{BZ} dk |cvk\rangle \langle cvk| + \ldots,
\]

(A12)

where \( |cvk\rangle \equiv \hat{a}^{\dagger}_{cvk} \hat{a}_{cvk} |gs\rangle \), \( |cvk, c_1 v_1 k_1\rangle \equiv \hat{a}^{\dagger}_{cvk} \hat{a}^{\dagger}_{c_1 v_1 k_1} \hat{a}_{c_1 v_1 k_1} |gs\rangle \), etc., we find

\[
\eta_{\nu R_2;\mu R_1}^{(1b)}(t) = \frac{\iota e}{\hbar} \frac{\Omega_{\nu c}}{(2\pi)^d} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha \beta R R'} \int_{BZ} dK e^{iK' \cdot (R' - R)} \tilde{\xi}_{\beta \alpha}^{a}(K') \left( \langle gs | \hat{a}^{\dagger}_{\beta R'}(t') \hat{a}_{\alpha R}(t') \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) | gs \rangle \right)
\]

\[
- \frac{\iota e}{\hbar} \frac{\Omega_{\nu c}}{(2\pi)^d} \int_{-\infty}^{t} dt' E^{\alpha}(t') \sum_{\alpha \beta R R'} \int_{BZ} dK e^{iK' \cdot (R' - R)} \tilde{\xi}_{\beta \alpha}^{a}(K') \left( \langle gs | \hat{a}^{\dagger}_{\beta R'}(t') \hat{a}_{\alpha R}(t') \hat{a}^{\dagger}_{\mu R_1}(t) \hat{a}_{\nu R_2}(t) | gs \rangle \right)
\]

\[
= \epsilon \frac{\Omega_{\nu c}}{(2\pi)^d} \sum_{\omega} e^{-i(\omega + i0^{+})t} E^{\alpha}(\omega) \int_{BZ} dk' \sum_{nm,k'} \frac{f_{nm,k'} e^{iK' \cdot (R_2 - R_1)} U^{\dagger}_{vn}(k') \xi_{mn}^a(k') + W_{mn}^a(k') U_{nm}(k')}{E_{mk'} - E_{nk'} - \hbar(\omega + i0^{+})}
\]

(A13)
Notably terms resulting from the first term of the completeness relation (A12), which would involve diagonal matrix elements, cancel one another. Then combining (A11) with (A13) and implementing (18), we find

\[
\eta^{(1)}_{\nu R_2;\mu R_1}(\omega) = e \frac{\Omega_{uc}}{(2\pi)^d} E^a(\omega) \int_{BZ} dk e^{ik\cdot(R_2-R_1)} \sum_{mn,k} f_{nm,k} U^\dagger_{vm}(k) \xi^a_{mn}(k) U_{nm}(k) \\
+ e \frac{\Omega_{uc}}{(2\pi)^d} E^a(\omega) \sum_{n} \int_{BZ} dk e^{ik\cdot(R_2-R_1)} f_{nk}((R_1 - R_n^0)U^\dagger_{vm}(k)U_{nm}(k) + i\partial_n(U^\dagger_{vm}(k)U_{nm}(k))) \\
- i e \frac{\Omega_{uc}}{(2\pi)^d} E^a(\omega) \sum_{n} \int_{BZ} dk e^{ik\cdot(R_2-R_1)} (\partial_n f_{nk}) U^\dagger_{vm}(k)U_{nm}(k),
\]

(A14)

where we have used an integration by parts for which the surface terms vanish. Notably the term in (A14) that diverges in the dc limit arises from the interaction term \(-e E^a(t) \sum_n R^a \hat{a}_{\nu R}(t)\hat{a}_{\alpha R}(t)\), the second term of (A7). At first one might suspect that it is the sum over Bravais lattice vectors \( R \) that leads to the dc divergence, or if not, some other divergence. But in fact this is not the case because in the linear response calculation the relevant objects are of the form \( \sum_n R^a \langle gs| \hat{a}_{\nu R}^\dagger(t)\hat{a}_{\alpha R}^\dagger(t')\hat{a}_{\alpha R}(t')|gs \rangle \) (see the first line of (A11)); thus not all \( R \)'s contribute equally and the result of such a sum appears to be finite.

To gain further insight into origin of the terms appearing in (A14), it is useful to rewrite \( \hat{V}_1(t) \) in terms of the operators that generate the single-particle electronic energy eigenvectors. The second term of (A7) involves

\[
\sum_{\alpha R} R^a \hat{a}_{\alpha R}^\dagger(t)\hat{a}_{\alpha R}(t) = \frac{i}{2} \int_{BZ} dk \sum_{n} \left( \hat{a}_{nk}^\dagger(t)(\partial_n \hat{a}_{nk}(t)) - (\partial_n \hat{a}_{nk}^\dagger(t))\hat{a}_{nk}(t) \right) - \int_{BZ} dk \sum_{nm} \hat{a}_{nk}^\dagger(t)W_{nm}(k)\hat{a}_{mk}(t).
\]

(A15)

When implemented in the linear response calculation, the first two terms of (A15) give non-zero contributions only for those \( k \) “near” the Fermi surface and indeed gives vanishing contribution if \( |gs\rangle \) is the ground state of a trivial insulator. That such an interaction term leads to a diverging induced free current density is in-line with physical expectation. The first term of (A7) can also be rewritten,

\[
\sum_{\alpha \beta RR'} \hat{a}_{\alpha R}^\dagger(t)\hat{a}_{\beta R'}(t) \int_{BZ} dk e^{ik\cdot(R-R')} \hat{\xi}_{\alpha \beta}(k) = \frac{(2\pi)^d}{\Omega_{uc}} \int_{BZ} dk \sum_{nm} \hat{a}_{nk}^\dagger(t)\left( \xi_{nm}(k) + W_{nm}(k) \right)\hat{a}_{mk}(t).
\]

(A16)

The net result is

\[
\hat{V}_1(t) = -e \frac{\Omega_{uc}}{(2\pi)^d} E^a(t) \sum_{\alpha \beta RR'} \hat{a}_{\alpha R}^\dagger(t)\hat{a}_{\beta R'}(t) \int_{BZ} dk e^{ik\cdot(R-R')} \hat{\xi}_{\alpha \beta}(k) - e E^a(t) \sum_{\alpha R} R^a \hat{a}_{\alpha R}^\dagger(t)\hat{a}_{\alpha R}(t)
\]

\[
= -e E^a(t) \int_{BZ} dk \sum_{nm} \hat{a}_{nk}^\dagger(t)\xi_{nm}(k)\hat{a}_{mk}(t) + \frac{ie}{2} E^a(t) \int_{BZ} dk \sum_{n} \left( (\partial_n \hat{a}_{nk}^\dagger(t))\hat{a}_{nk}(t) - (\partial_n \hat{a}_{nk}^\dagger(t))\hat{a}_{nk}(t) \right),
\]

which is gauge independent, as expected. As described above, due to the relative negative sign between terms involving \( \hat{V}_1(t) \) and \( \hat{V}_1^T(t) \) in the perturbative expansion of the electron Green function, the interaction term involving \( E^a(t) \int_{BZ} dk \sum_{nm} \hat{a}_{nk}^\dagger(t)\xi_{nm}(k)\hat{a}_{mk}(t) \) gives rise only to terms for which \( n \neq m \), which we refer to as being related to the “interband response”. See e.g., the cancellation of “intraband” terms in (A13). In contrast we refer to the terms resulting from the interaction term involving \( iE^a(t) \int_{BZ} dk \sum_{n} \left( \hat{a}_{nk}^\dagger(t)(\partial_n \hat{a}_{nk}(t)) - (\partial_n \hat{a}_{nk}^\dagger(t))\hat{a}_{nk}(t) \right) \) as being related to the “intraband response”.

Appendix B: Time-reversal symmetry

Taking \( T |\psi_{nk}\rangle = e^{-i\lambda_n(k)} |\psi_{n-k}\rangle \) [2], which is equivalent to \( \psi^*_{nk}(x) = T \psi_{nk}(x) = e^{-i\lambda_n(k)} \psi_{n-k}(x) \), or alternatively \( u^*_{nk}(x) = e^{-i\lambda_n(k)} u_{n-k}(x) \), yields

\[
\xi_{nm}^a(k) = e^{i(\lambda_m(k) - \lambda_n(k))} \xi_{mn}^a(-k) - \delta_{nm} \partial \lambda_m(k)/\partial k^a,
\]

(B1)
and as well $E_{nk} = E_{n-k}$, which implies $f_{nk} = f_{n-k}$. Furthermore, time-reversal symmetry allows the ELWFs to be chosen such that they are real-valued functions \cite{22, 50}, and taking $W_{\alpha \mathbf{R}}(\mathbf{x}) \xlongequal{T} W_{\alpha \mathbf{R}}^*(\mathbf{x})$ yields

$$U_{\alpha n}(k) \xlongequal{T} U_{\alpha n}^*(-k)e^{-i\lambda_n(-k)},$$

which leads to

$$\mathcal{W}_{nm}^\alpha(k) \xlongequal{T} e^{i(\lambda_n(-k) - \lambda_n(-k))} \mathcal{W}_{nm}^\alpha(-k) - \delta_{nm} \frac{\partial \lambda_n(-k)}{\partial (-k)^i}.$$  \hfill (B2)

With these relations one can show

$$\int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \partial_t \left( \xi^{\alpha}_{mn}(k) + \mathcal{W}_{mn}^\alpha(k) \right) = -\int_{BZ} \frac{dk}{(2\pi)^d} \sum_n f_{nk} \partial_t \left( \xi^{\alpha}_{mn}(k) + \mathcal{W}_{mn}^\alpha(k) \right),$$

and therefore vanishes. It then immediately follows that $J_{\beta}^{(1)}(\omega = 0) \xlongequal{T} 0$, or equivalently that the term in (29) that diverges in the dc limit vanishes. Moreover from the relations (B1,B2) it follows that $M^{(0)} \xlongequal{T} 0$.

**Appendix C: Link currents and the related free current density**

Recall from past work \cite{13} that in the “long-wavelength limit”

$$H_{\alpha \mathbf{R'}, \lambda \mathbf{R}'}(\omega) = \int W_{\alpha \mathbf{R}'}^*(\mathbf{x}) H_0(\mathbf{x}, \mathbf{p}(\mathbf{x})) W_{\lambda \mathbf{R}}(\mathbf{x}) - \frac{e}{2} \int W_{\alpha \mathbf{R}'}^*(\mathbf{x}) \left((\mathbf{x} - \mathbf{R}') + (\mathbf{x} - \mathbf{R})\right) \cdot E(t) W_{\lambda \mathbf{R}}(\mathbf{x}),$$  \hfill (C1)

and since we write $H_{\alpha \mathbf{R'}, \lambda \mathbf{R}'}(\omega) = H_{\alpha \mathbf{R'}, \lambda \mathbf{R}'}^{(0)} + H_{\alpha \mathbf{R'}, \lambda \mathbf{R}'}^{(1)}(\omega)$, with all higher order contributions vanishing in this case, we identify

$$H_{\alpha \mathbf{R'}, \lambda \mathbf{R}'}^{(0)} = \int W_{\alpha \mathbf{R}'}^*(\mathbf{x}) H_0(\mathbf{x}, \mathbf{p}(\mathbf{x})) W_{\lambda \mathbf{R}}(\mathbf{x}),$$  \hfill (C2)

$$H_{\alpha \mathbf{R'}, \lambda \mathbf{R}'}^{(1)}(\omega) = -\frac{e}{2} \int W_{\alpha \mathbf{R}'}^*(\mathbf{x}) \left((\mathbf{x} - \mathbf{R}') + (\mathbf{x} - \mathbf{R})\right) \cdot E(t) W_{\lambda \mathbf{R}}(\mathbf{x}).$$  \hfill (C3)

With this we implement the definition of $I(R, R'; \omega)$ previously given, and with (19) we find

$$I^{(1)}(R, R'; \omega) = \frac{e}{\hbar} \sum_{\alpha \lambda} \left( H_{\alpha \lambda \mathbf{R}, \lambda \mathbf{R}}^{(1)}(\omega) \eta_{\alpha \lambda \mathbf{R}, \alpha \mathbf{R}}^{(0)} - \eta_{\alpha \lambda \mathbf{R}, \lambda \mathbf{R}}^{(0)} H_{\alpha \lambda \mathbf{R}, \alpha \mathbf{R}}^{(1)}(\omega) \right) + \frac{e}{\hbar} \sum_{\alpha \lambda} \left( H_{\alpha \lambda \mathbf{R}, \lambda \mathbf{R}}^{(0)} \eta_{\alpha \lambda \mathbf{R}, \alpha \mathbf{R}}^{(1)}(\omega) - \eta_{\alpha \lambda \mathbf{R}, \lambda \mathbf{R}}^{(1)}(\omega) H_{\alpha \lambda \mathbf{R}, \alpha \mathbf{R}}^{(0)} \right)$$

$$= 2e^2 \left( \frac{\Omega_{uc}}{2\pi} \right)^2 E^t(\omega) \sum_{\alpha \lambda} \int_{BZ} d\mathbf{k} d\mathbf{k'} \mbox{Im} \left[ e^{i(k-k') \cdot (R-R')} \sum_{n} f_{nk} U_{\alpha n}(k') \xi^{\alpha}_{\lambda n}(k) U_{\alpha \lambda}(k') \right]$$

$$+ \frac{e^2}{\hbar} \left( \frac{\Omega_{uc}}{2\pi} \right)^2 E^t(\omega) \sum_{\alpha \lambda} \int_{BZ} d\mathbf{k} \sum_{s} \int_{BZ} d\mathbf{k'} \frac{E_{sk}}{\hbar(\omega + i0^+)}$$

$$\times \left( e^{i(k-k') \cdot (R-R')} U_{\alpha \lambda}(k) \sum_{n} f_{nk} \left( (R'-R)U_{\alpha n}(k') U_{\alpha \lambda}(k') + i\partial_t (U_{\alpha \lambda}(k') U_{\alpha n}(k')) \right) U_{\alpha \lambda}(k) \right) \left( e^{i(k-k') \cdot (R-R')} U_{\alpha n}(k) \sum_{m} f_{nm} U_{\alpha m}(k) U_{\alpha \lambda}(k) U_{\alpha \lambda}(k') \right)$$

$$- e^{-i(k-k') \cdot (R-R')} U_{\alpha \lambda}(k) \sum_{n} f_{nk} \left( (R'-R)U_{\alpha n}(k') U_{\alpha \lambda}(k') + i\partial_t (U_{\alpha \lambda}(k') U_{\alpha n}(k')) \right) U_{\alpha \lambda}(k).$$  \hfill (C4)

The first line of (C4) is the result of a “compositional” modification, while the remainder is the result of a “dynamical” modification; the second term of (32) is the result of the first term of (19) and the final term of (32) is the result of
the second term of (19). Notably the first line of (32) is independent of energy and involves frequency only through $E(\omega)$, while this is generally not the case for the other terms.

In Sec. IV we are interested, among other things, in the macroscopic free current density, $J_F^i(x, \omega)$, related to the microscopic free current density $j_F^i(x, \omega)$. In past work [20] we have described this averaging procedure in some detail, in particular for the microscopic polarization and magnetization fields. In the limit of a uniform applied electric field, the expressions Eq. (7), (9), (B4)-(B6), and (B8) presented there result in the macroscopic polarization and magnetization fields. We here focus on the macroscopic free current density $j_F^i(x, \omega)$ by implement a spatial averaging function $w(x)$ to relate the microscopic and macroscopic quantities. That is, $\nabla \times J_F^i(x, \omega) \equiv \int w(x - x') j_F^i(x', \omega) dx'$.

Implementing the definition (31), the relator expansion [20]

$$s'(w; x, y) \simeq (x^i - y^i) \delta(w - y) - \frac{1}{2}(x^i - y^i)(x^j - y^j) \frac{\partial \delta(w - y)}{\partial w^j} + \ldots,$$

and noting that the first-order modification to the link currents here takes the form $I^{(1)}(R, R'; \omega) = I^{(1)}(R - R', \omega)$, we find

$$J_F^{i(1)}(x, \omega) = \frac{1}{2} \sum_{RR'} I^{(1)}(R - R', \omega) \left((R^i - R'^i) w(x - R) + \frac{1}{2}(R^i - R'^i)(R'^j - R'^j) \frac{\partial w(x - R)}{\partial x^j} + \ldots\right)$$

$$= \frac{1}{2} \sum_{R_1} I^{(1)}(R_1, \omega) \left(R_1^i \sum_R w(x - R) + \frac{1}{2}R_1^i R_1^j \frac{\partial w(x - R)}{\partial x^j} \sum_R w(x - R) + \ldots\right)$$

$$= \frac{1}{2\Omega_{uc}} \sum_{R_1} I^{(1)}(R_1, \omega) R_1^i,$$

where in going to the final line we have used the special case of a uniform applied electric field in Eq. (B8) of [20]. Thus, we arrive at (33).

[14] As previously discussed [13], for the periodic systems that are the primary focus of this work, the set of “sites” – which is a non-unique collection of positions within the material medium about which localized portions of the charge and current densities might be identified – is chosen to coincide with a choice of Bravais lattice that characterizes the crystal structure of the medium of interest. We refer to the elements of such a set of sites as “lattice sites”, and with this choice each such lattice site is itself a Bravais lattice vector.
[15] For the electric and magnetic multipole moments that will follow from $\rho_R^i(x, t)$ and $j_R(x, t)$ to be well-defined to arbitrary order, the set of basis functions must decay faster than any polynomial.
Here by “compete set” of ELWFs we mean span_{C}(\{ | \alpha \rangle R | \alpha \in \{1, 2, \ldots \}, R \in \Gamma \}) \cong \text{Hilb} \text{span}_{C}(\{| \psi_{nk} \rangle | H_{0} | \psi_{nk} \rangle = E_{nk} | \psi_{nk} \rangle \}), for \Gamma \subset \mathbb{R}^d a Bravais lattice of the relevant crystalline solid.

Technically, we refer to the Hilbert bundle \((B, \pi, \text{BZ})\) over the Brillouin zone torus with fibers \(\pi^{-1}(\{ k \})\) being the infinite dimensional Hilbert space spanned by the electronic energy eigenvectors identified with \( k \in \text{BZ} \) as the Bloch bundle. That such a construction indeed results in a fiber bundle has been shown \([24, 51]\).

For the case of finite-rank vector bundles, see, e.g., Corollary 10.20 of \([52]\).

The crucial statement is that infinite-rank Hilbert bundles are trivializable; see Appendix D of \([24]\).

This follows from the fact that a vector bundle is trivializable if and only if the canonical principal bundle constructed using its frames is also trivializable. See, e.g., Proposition A.9 of \([53]\).

For case where \( d = 2 \), see, e.g., Eq. (1.14) of \([54]\).

It immediately follows that the analogous Hilbert bundle constructed using the eigenvectors associated with the conduction bands is also trivial.

[18] In past work \([13]\) we implemented a different notation; there we identified what we here denote \( p^{\alpha}_{R}(x, t) \) with the symbol \( p_{R}(x, t) \) and \( \rho^{\alpha}_{R}(x, t) \) with the symbol \( \rho_{R}(x, t) \). In later work \([20]\) we implement the notation used here.


[26] Here by “compete set” of ELWFs \( W_{\alpha}(x) \equiv \langle x | \alpha \rangle R \) we mean span_{C}(\{ | \alpha \rangle R | \alpha \in \{1, 2, \ldots \}, R \in \Gamma \}) \cong \text{Hilb} \text{span}_{C}(\{| \psi_{nk} \rangle | H_{0} | \psi_{nk} \rangle = E_{nk} | \psi_{nk} \rangle \}), for \Gamma \subset \mathbb{R}^d a Bravais lattice of the relevant crystalline solid.

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[35] It immediately follows that the analogous Hilbert bundle constructed using the eigenvectors associated with the conduction bands is also trivial.


[37] See, e.g., \([55]\).

[38] In past work this object taken a more abstract form, but in the long-wavelength limit the more simple expression presented here is admitted. See discussion in Appendix A.

[39] The operators \( a_{nk}(t) \) and \( a_{nk}^\dagger(t) \) appearing in interaction terms evolve in the interaction picture. For details, see Appendix A.


[41] See, e.g., \([44]\), \([56]\), and references therein.


[45] See, e.g., Eq. 13.36 of \([57]\).


[47] See, e.g., Chapter 6 of \([58]\).


[49] See, e.g., \([59]\).


